

Bell Road, Clement Town Dehradun-248002 Uttarakhand Ph. : 0135-2644183, 2642799, Fax : 0135-2644025 www.geu.ac.in



Department of Electronics and Communication Engineering

Master of Technology

Electronics and Communication Engineering

VLSI Design and Systems

Curriculum



# University Vision

We visualize Graphic Era (Deemed to be University) as an internationally recognized, enquiry driven, ethically engaged diverse community, whose members work collaboratively for positive transformation in the world, through leadership in teaching, research and social action.

# **University Mission**

The mission of the university is to promote learning in true spirit and offering knowledge and skills in order to succeed as professionals. The university aims to distinguish itself as a diverse, socially responsible learning community with a high-quality scholarship and academic rigor.

# **Department Vision**

The Department visualizes itself to become leading centre of learning in the field of Electronics & Communication Engineering with academic excellence in research to produce self-motivated, creative, and socially responsible engineers and specialists, ready to take up challenges of industrial development with ethics and societal commitment.

# **Department** Mission

**M1:** To provide high quality contemporary education in the field of Electronics & Communication Engineering and professional ethics to its learners.

*M2:* To provide creative learning environment for the students to equip them with strong foundation for continuing higher education.

*M3:* To pursue research and develop insight knowledge of current and emerging technologies in Electronics & Communication Engineering to serve the needs of the society, industry, and scientific community.

*M4:* To prepare students to have creative and innovative thinking to develop them into socially responsible professionals

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Progra	<b>Program Educational Objectives (PEOs):</b>							
<b>PEO</b> 1	Implementation of core-engineering knowledge to solve practical problems in the areas of VLSI design and Systems, and to produce innovative systems in these domains.							
<b>PEO 2</b>	Motivating entrepreneurship in VLSI domains by integration of sustainability with efficiently designed systems.							
<b>PEO 3</b>	Sharpening the educational, and research-oriented skills of the students for their easy merger into a future career in research or academia.							
PEO 4	Developing the design engineers with excellent ability to communicate, along with a morally responsible behavior.							



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Program	Outcomes (POs):
<b>PO1</b>	Apply the knowledge of science, mathematics, and engineering principles for developing problem solving attitude.
<i>PO2</i>	Identify, formulate, and solve engineering problems in the broad areas like System Design using VLSI.
РО3	Use different modern engineering software tools in the domain of VLSI and Systems Design.
<b>PO</b> 4	Design and conduct experiments, analyze and interpret data, imbibe programming skills for development of simulation experiments.
<i>PO5</i>	Function as a member of a multidisciplinary team with sense of ethics, integrity, and social responsibility.
<b>PO6</b>	Realize the need for self-education and ability for independent and life-long learning.

Program Specific outcomes (PSOs):						
PSO1	Attain competency in areas of IC designing, testing, and developing prototype of various VLSI circuits.					
PSO2	Integrating various VLSI sub-systems to design industrial circuits.					
PSO3	Students gain skills in developing various complicated circuits and excel in industrial sector.					



## **Department of Electronics and Communication Engineering**

### **Course Components of Postgraduate Programme**

### **Definition of Credits**

	1 Hr. Lecture (L) per week	1 credit					
	1 Hr. Tutorial (T) per week	1 credit					
	1 Hr. Practical (P) per week	0.5	credit				
	2 Hours Practical (P) per week	1 0	credit				
S. No.	Category	Abbreviation	Break-up of credits (M. Tech- VLSI Design and Systems)				
1.	Program Core	РС	34				
2.	<b>Program Elective courses relevant to chosen</b> specialization/branch	PE	09				
3.	Open subjects–Electives from other technical and/or emerging subjects	OE	03				
4.	Project work, seminar and internship in industry or appropriate workplace/ academic and research institutions in India/abroad	PROJ	28				
5.	General Proficiency*	GP	04				
	1	Total	78				

\*Institution Initiative



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## **Program Course Structure (All Semesters)**

M. Tech (VLSI Design and Systems)

(Batch 2023 onwards)

#### Semester I

	Course Module				Te	eachii	ng		Weig	htage	•
		COURSE				Period	0			uation	
S. No.	Code	Course title	Component	Credits	L	Т	Р	CIE	MSE	SEE	Total
1	VDM 101	Semiconductor Materials and Devices	РС	3	3	0	0	25	25	50	100
2	VDM 102	CMOS Analog Circuit Design	РС	3	3	0	0	25	25	50	100
3	VDM 103	Advanced Digital Integrated Circuit	РС	3	3	0	0	25	25	50	100
4	VDM 104	VLSI Technology	РС	3	3	0	0	25	25	50	100
5	VDM -	Program Elective-I	PE	3	3	0	0	25	25	50	100
		Laboratory and Others									
6	VDM 151	CMOS Analog Circuit Design Lab	РС	2	0	0	4	25	25	50	100
7	VDM 152	Digital VLSI Circuit Design Lab	РС	2	0	0	4	25	25	50	100
8	GP101	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		20	15	00	08				800



#### M. Tech (VLSI Design and Systems)

(Batch 2023 onwards)

#### Semester II

Course Module				Te	eachii	ng		Weig	htage	:	
		COURSE				Perioa			Evaluation		
S. No.	Code	Course title	Component	Credits	L	Т	Р	CIE	MSE	SEE	Total
1	VDM 201	Advanced ASIC and FPGA Design	РС	3	3	0	0	25	25	50	100
2	VDM 202	Digital System Design using Verilog HDL	РС	3	3	0	0	25	25	50	100
3	VDM 203	Advanced VLSI Circuit Testing	РС	3	3	0	0	25	25	50	100
4	VDM 204	Low Power VLSI Design	РС	3	3	0	0	25	25	50	100
5	VDM	Program Elective- II	PE	3	3	0	0	25	25	50	100
		Laboratory and Oth	ers								
6	VDM 251	Verilog HDL Lab	РС	2	0	0	4	25	25	50	100
7	VDM 252	VLSI Physical Design Lab	РС	2	0	0	4	25	25	50	100
8	VDM 253	Mini Project with Seminar	PROJ	2	0	0	4	25	0	75	100
9	GP 201	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		22	15	00	12				900





#### M. Tech (VLSI Design and Systems)

(Batch 2023 onwards)

Semester III

Course Module			Т	eachir	ıg		<b>1</b> /	F	<b>I</b> (•		
		COURSE		Periods Weightage: E			e: Eva	aluation			
S. No.	Code	Course title	Component	Credits	L	Т	Р	CIE	MSE	SEE	Total
1	VDM	Program Elective- III	PE	3	3	0	0	25	25	50	100
2	VOM	<b>Open Elective</b>	OE	3	3	0	0	25	25	50	100
		Laboratory and Oth	ers								
3	VDM 351	Modelling and Simulation Lab	РС	2	0	0	4	25	25	50	100
4	VDM 301	Dissertation Phase-I*	PROJ	10	0	0	20	25	50	125	200
5	GP 301	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		19	06	00	24				600

\*Students going for Industrial Project/Thesis will complete these courses through MOOCs.



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#### M. Tech (VLSI Design and Systems)

(Batch 2023 onwards)

Semester IV

	COURSE			Teaching Periods			Weightage: Evaluation				
S. No.	Code	Course title	Component	Credits	L	Т	Р	CIE	MSE	SEE	Total
1	VDM 401	Dissertation Phase-II	PROJ	16	0	0	32	50	100	250	400
2	GP 401	General Proficiency	GP	1	0	0	0	0	0	100	100
		TOTAL		17	00	00	32				500



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M. Tech (VLSI Design and Systems) (Batch 2023 onwards) Program Electives and Open Electives

	<b>Program Elective Courses</b>					
Course Code	Course Name	Semester				
	<b>Program Elective I</b>					
VDM 191	Advanced Nanotechnology					
VDM 192	<b>Optimization Techniques in VLSI Design</b>					
VDM 193	Theory and Application of Embedded Systems					
VDM 194	Digital Signal Processing for VLSI	First				
VDM 195	Robust Control System					
<i>VDM 196</i>	Control of Advanced Electric Machine					
	<b>Program Elective II</b>					
VDM 291	Micro-Sensors and MEMS					
VDM 292	<b>RF</b> Microelectronics Devices					
VDM 293	VLSI Circuits for Biomedical Application					
VDM 294	Microwave & MM-wave Integrated Circuits and Applications	Second				
VDM 295	Renewable Energy Resources and Energy Management					
VDM 296	Multivariable Control System	-				
	<b>Program Elective III</b>					
VDM 391	Organic Electronics Devices and Circuits					
VDM 392	Memory Design and Testing					
VDM 393	System on Chip Design and Testing	Third				
VDM 394	VLSI Physical Design Automation					
<i>VDM 395</i>	Power Quality Assessment					
<i>VDM 396</i>	<b>Optimal &amp; Adaptive Control</b>					





	<b>Open Elective Courses</b>						
Course Code	Course Name	Semester					
VOM 301	Cloud Computing						
VOM 302	Internet of Things	<i>T</i> T1 • 1					
VOM 303	Artificial Intelligence and expert systems	Third					
VOM 304	Soft Computing						
Allenaviat		-					

#### Abbreviations:

L	Lecture
Τ	Tutorial
Р	Practical
CWA	Class Work Assessment
MSE	Mid Semester Exam
ESE	End Semester Exam
PC	Program Core
PE	Program Elective
OE	Open Elective
PROJ	Project
GP	General Proficiency*

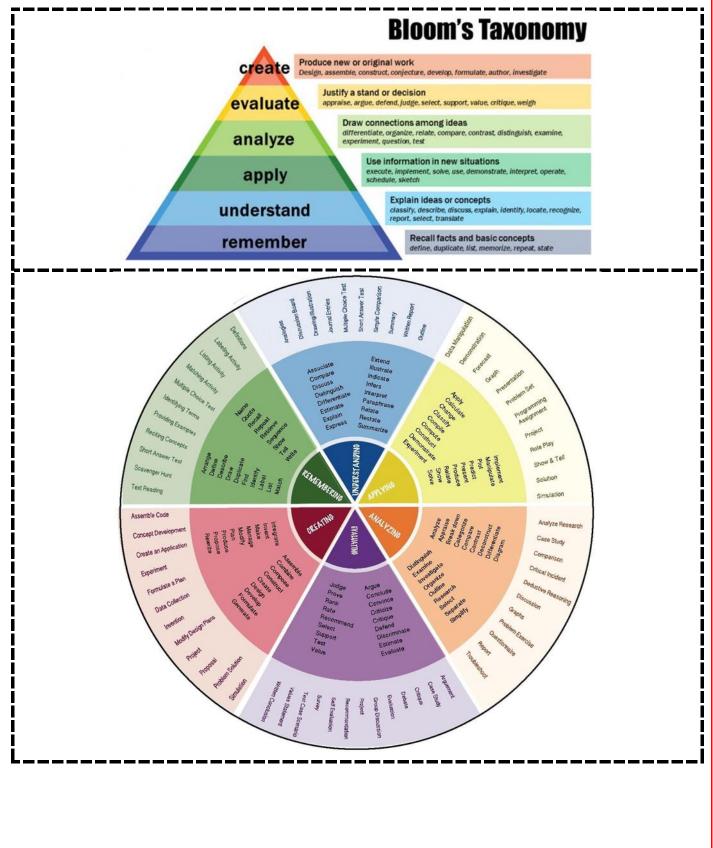
\*Institution Initiative



## **Bloom's Taxonomy for Curriculum Design and Assessment**

Preamble

The design of curriculum and assessment is based on Bloom's Taxonomy. A comprehensive guideline for using Bloom's Taxonomy is given below for reference.





		SEM	ESTER I				
<b>S.</b> No.	Department of Electronics and Communication Engineering						
1.	Subject Code	VDM 101	C	ourse Title	Semicor	nductor Ma Devices	iterials and
2.	<b>Contact Hours</b>	L	3	Т	0	Р	0
3.	Examination Duration	Theory		3	Practi	cal	0
4.	Relative Weight	CIE	25	MSE	25	SEE	50
6.	Credit			6	)3		
6.	Semester			Fi	irst		
7.	Category of Course	РС					
8.	Pre-requisite	Basic Electronics Engineering (TEC-101/201), Electronic Devices and Circuits (TEC-301)					

9.	Course Outcomes	After completion of the course the students will be able to: CO1: <b>Create</b> basic understanding of semiconductor device physics. CO2: <b>Evaluate</b> two terminal MOS structure in terms of its electrical parameters.
		CO3: Analyse the three terminal MOS structure in terms of electrical potential and charge. CO4: Apply surface potential and charges in different regions of MOSFET operation. CO5: Understand the short channel and narrow channel effects. CO6: Implement the concepts of semiconductor device physics in developing real life applications.

<i>S. No.</i>	Contents	<b>Contact Hours</b>
1.	Unit 1: Basics of Semiconductors: Semiconductor materials, Energy levels, Intrinsic and extrinsic semiconductor, Equilibrium in absence/presence of electric field.	8
2.	<b>Unit 2: PN Junction Diode:</b> Junction diode: PN junction, Tunnel diode, Quasi-fermi levels, Depletion width capacitance and its application in doping profile determination, I-V characteristics of narrow and wide base diodes and their equivalent circuits, Breakdown mechanisms, Small signal ac impedance.	0
3.	Unit 3: Two Terminal MOS Structure:	10



	Flat band voltage, Potential balance and charge balance, Effect of gate body voltage on surface condition, Accumulation, Depletion, Inversion, General analysis, Small signal capacitance.	
4.	Unit 4: Three Terminal MOS Structure: Contacting the inversion layer, Body effect, Different regions of operation, Pinch-off voltage.	10
5.	Unit 5: Four Terminal MOS Structure: Transistors regions of operation, Complete all-region model, Simplified all-region model, Models based on quasi fermi potential, Regions of inversion in terms of terminal voltage, Temperature effects, Breakdown, Enhancement mode, Depletion mode transistors.	6
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	<i>Tsividis, Yannis, and Colin McAndrew, "Operation and Modelling of the</i> <i>MOS Transistor", Oxford: Oxford University Press, Vol. 2, 3<sup>rd</sup> Edition, 2003.</i>	3 <sup>rd</sup>	2003
2.	S. Kang and Y. Leblebici, "CMOS Digital Integrated Circuits, Analysis and Design", 3 <sup>rd</sup> Edition, Tata McGraw-Hill, 2003.	3 <sup>rd</sup>	2003
	Reference Books		
1.	Adel S. Sedra, Kenneth C. Smith, " Microelectronic Circuits", Oxford University Press	$7^h$	2014
2.	S. Salivahanan and S. Arivazhagan, "Digital Circuits and Design", Oxford University Press,	5 <sup>th</sup>	2008
3.	Robert L. Boylestad and Louis Nashelsky, "Electronic Devices and Circuit Theory", Prentice Hall of India (PHI).	$9^{th}$	2006

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SE	MEST	ER I				
<i>S. No.</i>	<b>Department of Electronics and Communication Engineering</b>							
1.	Subject Code	VDM 1	02	Co	urse Title	CMOS A	Analog Cir	cuit Design
2.	Contact Hours	L	3		Т	0	Р	0
3.	Examination Duration	Theor	y		3	Practio	cal	0
4.	Relative Weight	CIE	2.	5	MSE	25	SEE	50
6.	Credit	03						
6.	Semester	First						
7.	Category of Course	РС						
8.	Pre-requisite		Electronics Devices and Circuits (TEC 301)					

9. Course Outcom	CO1: <b>Recall</b> the knowledge of analog IC design in CMOS technologies.
	<ul> <li>CO2: Understand MOS transistors with different configurations.</li> <li>CO3: Apply the concepts of multistage and differential MOS amplifiers.</li> <li>CO4: Analyse the current mirror circuits.</li> <li>CO5: Assess and evaluation the feedback amplifiers and phase locked loop.</li> <li>CO6: Design and develop various CMOS analog circuits.</li> </ul>

<i>S. No</i> .	Contents	Contact Hours
1.	Unit 1: Models for Integrated Circuit Active Devices: The depletion region of a PN junction, Depletion region capacitance and junction breakdown, Basics of MOS transistor, Derivation of current-voltage relationship, Analysis of MOS as an amplifier, Small signal models of MOS transistor, MOS transistor frequency response.	8
2.	Unit 2: Single Stage Amplifier: Common source stage with resistive load, CS stage with diode connected load, CS stage with current source load, CS stage with triode load, CS stage with source generation, Source follower and common gate configuration.	9
3.	Unit 3: Multistage Amplifier and Operational Amplifier: Cascode current source, Cascode amplifier, Differential pair, Small and large signal analysis of differential amplifier, Differential amplifier with MOS loads, OPAMP design: General consideration, One stage OpAmp	9
4.	Unit 4: Current Mirrors, Active Loads and References:	9



	Simple current mirror, Cascode current mirror, Wilson current mirror, Common source amplifier with complementary load, Voltage and current references: Widlar and peaking current sources, supply insensitive biasing	
5.	Unit 5: Feedback and Non-Linear Analog Circuits: General consideration, Properties of feedback circuits, Feedback configuration, Nonlinear analog circuits: LC oscillators, Simple phase locked loop.	9
	Total	44

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	B. Razavi, Design of analog CMOS Integrated Circuits, McGraw-Hill	$I^{st}$	2002
2.	Mohammed Ismail and Terri Faiz, Analog VLSI Signal and Information Process, McGraw-Hill.	I <sup>st</sup>	1994
	Reference Books		
1.	Paul R. Gray and R. G. Meyer, Analysis and Design of Analog Integrated Circuits, John Wiley and Sons	$4^{th}$	2001
2.	R. Jacob Baker, H. W. Li, and D.E. Boyce, CMOS: Circuit Design, Layout and Simulation, Prentice-Hall of India	3 <sup>rd</sup>	2010

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SE	MEST	ER I				
S. No.	Department of Electronics and Communication Engineering							
1.	Subject Code	VDM 1	VDM 103 Course Title Advanced Digit Circu				0	
2.	Contact Hours	L	Ĵ	}	Т	0	P	0
3.	Examination Duration	Theory	V		3	Practio	cal	0
4.	Relative Weight	CIE	2	5	MSE	25	SE	E 50
6.	Credit		03					
6.	Semester		First					
7.	Category of Course	РС						
8.	Pre-requisite	Bas	<b>Basic Electronics Engineering and Digital Electronics</b>					

9.	Course Outcomes	After completion of the course the students will be able to: CO1: <b>Describe</b> the basic MOS structure and layout design CO2: <b>Understand</b> the static and dynamic characteristics of MOS inverters CO3: <b>Apply</b> the MOS concepts to design combinational and sequential MOS
		logic circuits. CO4: <b>Analyze</b> different digital MOS logic circuits.
		CO5: Estimate power consumption of CMOS logic circuits. CO6: Integrate various concepts of digital VLSI circuit design and apply them in designing of MOS based digital circuits.

<b>S.</b> No.	Contents	Contact Hours
1.	Unit 1: Introduction and Implementation of strategies for digital ICs: Issues in Digital Integrated Circuit Design, Quality Metrics of a Digital Design, Design rule: Stick diagram and layout. Custom Circuit design, Cell based, and Array based design implementations.	10
2.	<i>Unit 2: MOS Inverters:</i> <i>Static and Dynamic Characteristics of CMOS inverter, Power dissipation, Logical effort.</i>	10
3.	Unit 3: Designing combinational and sequential circuits: Static CMOS design, Different styles of logic circuits, Logical effort of complex gates, Static and dynamic properties of complex gates, Dynamic CMOS Logic. Timing metrics of sequential circuits, Dynamic latches and Registers. Pipelining.	10
4.	Unit 4: Interconnect and Timing Issues: Circuit characterization and performance estimation - Resistance, Capacitance estimation - Switching characteristics - Delay models – Timing issues in Digital circuits, Power dissipation. Impact of Clock Skew and Jitter.	6
5.	Unit 5: Memory Design:	6



	Read-Only Memories, ROM cells, Read-write memories (RAM), dynamic memory design,	
	6 transistor SRAM cell, Sense amplifiers	
	Total	42
11 0		

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	S. Kang and Y. Leblebici, "CMOS Digital Integrated Circuits, Analysis and Design", Tata McGraw-Hill.	3rd	2003
2.	J. M. Rabaey, A. Chandrakasan and B. Nikolic, "Digital Integrated Circuits: A Design Perspective", Prentice-Hall of India.	2nd	2006
	Reference Books		
1.	John P. Uyemura, "Introduction to VLSI Circuits", Wiley India Pvt. Ltd.	lst	2012
2.	Eugene Fabricius, "Introduction to VLSI Design", New Ed Edition, Tata McGraw - Hill Education.	lst	1990
3.	N. H. E. Weste et. al., "CMOS VLSI Design", Pearson.	3rd	2005
4.	R. Jacob Baker, "CMOS: circuit design, layout, and simulation", John Wiley & Sons,	3rd	2010

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER I

<i>S. No.</i>	<b>Department of Electronics and Communication Engineering</b>						
1.	Subject Code	VDM 1	04	Course Title	V	LSI Techno	logy
2.	Contact Hours	L	3	Т	0	Р	0
3.	Examination Duration	Theor	v	3	Practi	cal	0
4.	Relative Weight	CIE	25	MSE	25	SEE	50
6.	Credit	03					
6.	Semester	First					
7.	Category of Course	РС					
8.	Pre-requisite	<b>Basic Electronics Engineering and Digital Electronics</b>					

9. Course Outcomes	<ul> <li>After completion of the course the students will be able to:</li> <li>CO1: Explain about wafer fabrication techniques and oxidation process</li> <li>CO2: Analyse photolithography and etching techniques of VLSI design.</li> <li>CO3: Extend the knowledge of different physical and chemical deposition methods.</li> <li>CO4: Investigate metal deposition techniques and IC fabrication methodologies.</li> <li>CO5: Design and analysis of different packaging methods.</li> <li>CO6: Create a base for the semiconductor device fabrication using VLSI technology.</li> </ul>
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<i>S. No.</i>	Contents	<b>Contact Hours</b>
1.	Unit 1: Wafer Preparation and Oxidation: Electron grade silicon, Crystal growth, Wafer preparation, Processing considerations, Vapor phase epitaxy and molecular beam epitaxy, Film characteristics, SOI structure, Oxide formation, Kinetics, Oxidation systems, Dry and wet oxidation, Masks properties of SiO2, Oxidation defects, Redistribution of dopant at interface, Oxidation of poly silicon.	10
2.	Unit 2: Lithography and Etching: Optical, Electron, X-Ray and Ion Lithography methods, Positive and negative photo resist. Plasma properties, Size, Control, Etch mechanism, Etch techniques and equipment.	8
3.	Unit 3: Deposition and diffusion: Deposition process and methods, Diffusion in solids, Diffusion equation and Diffusion mechanisms, Flick's one-dimensional diffusion equation, Atomic diffusion mechanism, Measurement techniques, Range theory, Implant equipment, Ion implantation, Damage and annealing, Ion implantation systems.	8
4.	<b>Unit 4: Metallization and IC Fabrication:</b> Metallization and its applications, Process simulation of Ion implementation, Diffusion, Oxidation, Epitaxy, Lithography, Etching and deposition, Annealing shallow junction –	8



	High energy implantation, Physical vapours deposition patterning. NMOS, CMOS and bipolar IC technologies and IC fabrication.	
5.	<i>Unit 5: Packaging:</i> Analytical and assembly techniques and packaging of VLSI devices.	8
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	S. M. Sze, "VLSI Technology", McGraw Hill, 2nd Edition, 1988.	$2^{nd}$	1988
2.	W. Wolf, "Modern VLSI Design", Pearson, 3rd Edition, 2002.	3 <sup>rd</sup>	2002
	Reference Books		
1.	S. K. Gandhi, " <b>VLSI Fabrication Principles Silicon and Gallium</b> <b>Arsenide</b> ", Wiley-INDIA, 2nd Edition, 1994.	$2^{nd}$	1994
2.	Wai Kai Chen, "VLSI Technology", CRC press, 1st Edition, 2003.	$I^{st}$	2003

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SE	MEST	ER I					
<i>S. No.</i>	Departn	nent of Electronics and Communication Engineering							
1.	Subject Code	<b>VDM 1</b> .	VDM 151 Course Title CMOS Analog Circuit Design						
2.	Contact Hours	L	l	)	Т	0 P			
3.	Examination Duration	Theory 0		Practical 4					
4.	Relative Weight	CIE	2	5	MSE	25	SEE	E 50	
6.	Credit				0	2			
6.	Semester				Fi	rst			
7.	Category of Course	РС							
8.	Pre-requisite	Electron	nics D	evices	and Circuit	t, VLSI Te	chnology	and Design	

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Understand Cadence Virtuoso simulation tool.
		CO2: Design common source, common drain, and operational amplifier using
		Cadence tool.
		CO3: Simulate and analyse various CMOS based circuits using Cadence tool.
		CO4: Integrate the acquired knowledge for developing CMOS based circuits.

S. No.	List of problems for which student should develop program and execute in the Laboratory	Contact Hours
1.	Design a new cell view and build common source amplifier and create a symbol for the common source amplifier using 90 nm technology.	1
2.	Simulation of common source amplifier test circuit using common source amplifier symbol using 90 nm technology.	1
3.	Create a layout of common source amplifier using 90 nm technology.	2
4.	Design a new cell view and build common drain amplifier and create a symbol for the common drain amplifier using 90 nm technology.	1
5.	Simulation of common drain amplifier test circuit using common drain amplifier symbol using 90 nm technology.	1
6.	Create a layout of common drain amplifier using 90 nm technology.	2

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7.	Design a new cell view and build Differential amplifier and create a symbol for the Differential amplifier using 90 nm technology.	1
8.	Simulation of Differential amplifier test circuit using Differential amplifier symbol using 90 nm technology.	I
9.	Create a layout of Differential amplifier using 90 nm technology.	2
10.	Design a new cell view and build operational amplifier and create a symbol for the operational amplifier using 90 nm technology.	I
11.	Simulation of operational amplifier test circuit using operational amplifier symbol using 90 nm technology.	1
12.	Create a layout of operational Amplifier using 90 nm technology.	2
	Total	16
	Innovative Experiments	
13.	Design and simulation of current mirror circuits using 90 nm technology.	2
14	Design and Simulation of Cascode amplifier using 90 nm technology.	2
	Total	04
1. Sug	gested Books	

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	B. Razavi, Design of analog CMOS Integrated Circuits, McGraw-Hill	$I^{st}$	2002
2.	Paul R. Gray and R. G. Meyer, Analysis and Design of Analog Integrated Circuits, John Wiley and Sons	$4^{th}$	2001
3.	Mohammed Ismail and Terri Faiz, Analog VLSI Signal and Information Process, McGraw-Hill <b>Reference Books</b>	$I^{st}$	1994
	Reference Dooks		
1.	<i>R. Jacob Baker, H. W. Li, and D.E. Boyce, CMOS: Circuit Design, Layout and Simulation, Prentice-Hall of India, 3rd Edition, 2010.</i>	3 <sup>rd</sup>	2010

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER I

<i>S. No.</i>	Departm	eent of Electronics and Communication Engineering							
1.	Subject Code	VDM 1	LSI Circuit	Circuit Design Lab					
2.	Contact Hours	L	0	Т	0	Р	4		
3.	Examination Duration	Theor	v	0	Practio	cal	4		
4.	Relative Weight	CIE	25	MSE	25	SEE	50		
6.	Credit		8		02				
6.	Semester			F	First				
7.	Category of Course	РС							
8.	Pre-requisite	Digital Electronics							

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Understand the CMOS based digital integrated circuits
		CO2: Analyze CMOS based combinational circuits using 180nmTechnology
		CO3: Evaluate CMOS based sequential circuits and memory devices.
		CO4: Design and validate various CMOS based digital circuits using Cadence
		tool

<i>S. No.</i>	List of problems for which student should develop program and execute in the Laboratory	Contact Hours
1.	Design and comparison of DC and transient output characteristics of CMOS inverter at different aspect ratio.	2
2.	Draw a layout of CMOS inverter using 45 nm technology and check for LVS and DRC for inverter circuit.	2
3.	Design and implement various gates with CMOS logic along with its layout.	2
4.	Draw a schematic of half adder/full adder using 45 nm technology and analyse its transient characteristics.	2
5.	Draw the layouts of half adder/full adder using 45 nm technology and simulate its transient characteristics.	2
6.	Design a schematic of comparator using 45 nm technology and simulate its transient characteristics	2
7.	Design and Implementation of 2:1 Multiplexer and 1:2 Demultiplexer.	2



8.	Design the schematic of latches using 45 nm technology and simulate its transient characteristics	2
9.	Design the schematic of flip-flops using 45 nm technology and simulate its transient characteristics	2
10.	Design the schematic of shift register using 45 nm technology and simulate its transient characteristics	2
11.	Design the schematic of up/down counter using 45 nm technology and simulate its transient characteristics	2
12.	Design the schematic of 6T RAM using 45 nm technology and simulate its transient characteristics	2
	Total	24
	Innovative Experiments	
13.	Design and implementation of Flash Memory with Cadence tool.	2
14.	Design and implementation of Different Analog to Digital converter (ADC) with Cadence tool.	2
15.	Simulate substrate bias (Body) effect in CMOS inverter.	2
		06

<i>11</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	Department of Electronics and Communication Engineering								
1.	Subject Code	VDM 201Course TitleAdvanced ASIC an Design							
2.	Contact Hours	L	3	}	Т	0	P	0	
3.	Examination Duration	Theor	v	3		Practi	cal	0	
4.	Relative Weight	CIE	2.	5	MSE	25	SE	E 50	
6.	Credit		<u>n</u>		0.	3	<u> </u>		
6.	Semester				Seco	ond			
7.	Category of Course	РС							
8.	Pre-requisite		Ŀ	4 <i>dvan</i>	ced Digital	Integrated	Circuit		

9.	<b>Course Outcomes</b>	After completion of the course the students will be able to:
		CO1: <b>Describe</b> the concepts of ASICs, CMOS Logic and ASIC Library Design.
		CO2: Understanding about partitioning, floor planning, placement and routing
		including circuit extraction of ASIC.
		CO3: Applying the concepts of ASIC and FPGA in designing various
		architecture of different types of FPGA.
		CO4: Analysis of the issues involved in ASIC design, including technology
		choice, design management, tool-flow, verification, debug and test, as well as
		the impact of technology scaling on ASIC design.
		CO5: Evaluation of SOC based integrated circuits for various FPGA
		applications.
		CO6: <b>Designing</b> of ASIC family using Xilinx tool to optimize the device
		performance.
		F J

#### 10. Details of the Course

<i>S. No.</i>	Contents	Contact Hours
1.	Unit 1: Introduction: Types of ASICs, Design flow, CMOS transistors CMOS design rules, Combinational logic cell, Sequential logic cell, Transistors as resistors, Transistor parasitic capacitance, Logical effort, Library cell design, Library architecture.	10
2.	<i>Unit 2: ASIC Physical Design:</i> <i>System partition, partitioning, partitioning methods, interconnect delay models and measurement of delay, floor planning, placement, Routing, Circuit extraction, Design Rule Check.</i>	9
3.	Unit 3: FPGA Architecture: Field Programmable gate arrays, Logic blocks, routing architecture, Design flow technology, Xilinx XC4000, ALTERA's FLEX 8000/10000, ACTEL's ACT-1,2,3 and their speed performance Case studies: Altera MAX 5000 and 7000, Altera MAX 9000, Spartan II and Virtex II FPGAs.	10

#### SEMESTER II



4.	Unit 4: Trade off issues at System Level: Optimization with regard to speed, area and power, asynchronous and low power system design. ASIC physical design issues, System Partitioning, Power Dissipation, Partitioning Methods.	8
5.	Unit 5: System on Chip Design: Design using Xilinx Family, System on Chip Design, SoC Design Flow, Platform based and IP based SoC designs, Basic Concept of Bus – Based communication architectures, On- chip communication architectures standards, Low power SoC designs.	8
	Total	45

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Pasricha and N. Dutt, " <b>On-Chip Communication Architectures System on</b> <b>Chip Interconnect</b> ", Elseveir.	1 <sup>st</sup>	2008
2.	Michael John Sebastian Smith, "Application-Specific Integrated Circuits", Addison-Wesley VLSI Systems Series	1 <sup>st</sup>	2008
	Reference Books		
1.	M. Rabaey, A. Chandrakasan, and B.Nikolic, "Digital Integrated Circuit Design Perspective", Wiley.	2 <sup>nd</sup>	2003
2.	Hoi-Jun Yoo, Kangmin Leeand Jun Kyong Kim, "Low-Power NoC for High- Performance SoC Design", CRC Press.	l <sup>st</sup>	2008

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		<b>SE</b> 1	MESTI	ER II				
<i>S. No.</i>	Departm	ent of Elec	tronic	s and	Communica	tion Engi	neering	
1.	Subject Code	VDM 2	02	Co	urse Title	Digital	System D Verilog H	esign using IDL
2.	Contact Hours	L	3	}	Т	0	Р	0
3.	Examination Duration	Theory	v		3	Practio	cal	0
4.	Relative Weight	CIE	2.	5	MSE	25	SEE	50
6.	Credit	03						
6.	Semester				Seco	ond		
7.	Category of Course	РС						
8.	Pre-requisite				Digital El	ectronics		

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Describe digital circuits and its implementation through Verilog HDL
		code.
		CO2: Understand the concept of logic synthesis using Verilog HDL, and its
		impact in verification.
		CO3: Design various combinational and sequential circuits.
		CO4: Analyse user defined primitives in Verilog HDL.
		CO5: Apply the knowledge of different types of digital modelling in Verilog
		HDL.
		CO6: Justify the implementation of Verilog code of several digital circuits using
		Verilog HDL and their test benches.

<b>S.</b> No.	Contents	<b>Contact Hours</b>
	Unit 1: Basic Concepts:	
	Lexical conventions, Data types, System tasks and compiler directives.	
1.	Modules and Ports:	8
	Modules, Ports, Hierarchical names.	
	Gate-Level Modeling:	
	Gate types, Gate delays.	
	Unit 2: Dataflow Modelling:	
	Continuous assignments, Delays, Expressions, Operators and Operands. Operator types,	
2.	Examples.	10
2.	Behavioural Modelling:	10
	Structured procedures, Procedural assignments, Timing controls, Conditional statements,	
	Multiway branching, Loops, Sequential and parallel Blocks, Generate blocks, Examples.	
	Unit 3: Task and Functions:	
3.	Differences between tasks and functions, Tasks, Functions.	8
	Useful Modelling Techniques:	

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	Procedural continuous assignments, Overriding parameters, Conditional compilation and execution, Time scales, Useful system tasks. <b>Timing and Delays:</b> Types of delay models, Path delay modelling, Timing checks, Delay back-annotation.	
4.	Unit 4: Switch-Level Modelling: Switch-Modelling elements, examples. User-Defined Primitives: UDP basics, Combinational UDPs, Sequential UDPs, UDP table shorthand symbols, Guidelines for UDP design.	8
5.	<b>Unit 5: Writing Test Benches:</b> Basic test benches, Test bench structure, Constrained random stimulus generation, Object- oriented programming and Assertion-based verification.	8
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Samir Palnitkar, "Verilog HDL", Pearson Education	$2^{nd}$	2003
2.	Mark Zwolinski, "Digital System Design with System Verilog", Pearson Education	$I^{st}$	2009
	Reference Books		
1.	J. Bhasker, "Verilog HDL Synthesis-A practical Prime", Star galaxy Press	1 <sup>st</sup>	1998
2.	J. Bhasker, "Verilog HDL Primer", Pearson Education"	3 <sup>rd</sup>	2015

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER II

S. No.	Departn	ent of Electronics and Communication Engineering							
1.	Subject Code	VDM 203 Course Title		Advanced VLSI Circuit Testing			it Testing		
2.	Contact Hours	L	Ĵ		Т	0	P	)	0
3.	Examination Duration	Theor	v		3	Practic	al		0
4.	Relative Weight	CIE	2	5	MSE	25	SE	E	50
6.	Credit	03							
6.	Semester	Second							
7.	Category of Course	РС							
8.	Pre-requisite		VLSI Technology						

9.	Course Outcomes	After completion of the course the students will be able to:			
		<i>CO1</i> : <i>Recall</i> the knowledge of fault modeling and fault simulation.			
		CO2: Understand ATPG algorithm for combinational and sequential circuits			
		CO3: Apply the knowledge of high-level testability Measures, SCOAP			
		controllability and observability.			
		CO4: Analyze different memory testing algorithms			
		CO5: Assess and evaluate scan architecture			
		CO6: <b>Design</b> testing algorithms for VLSI components			

<i>S. No.</i>	Contents	Contact Hours
1.	<ul> <li>Unit 1: Introduction: Role of testing, Digital and analog VLSI testing, VLSI technology trends affecting testing.</li> <li>VLSI Testing Process and Test Equipment: Types of testing, Automatic test equipment, Multi-Site testing, Electrical parametric testing.</li> <li>Test Economics and Product Quality: Defining costs, Production benefit-cost analysis, Economics of testable design, The rule of ten, Yield, Test data analysis.</li> <li>Fault Modelling: Defects, Errors and Faults, Functional versus Structural testing, A glossary of fault models, Single stuck-at fault, Logic and Fault Simulation: Simulation for design verification, Simulation for test evaluation.</li> </ul>	10
2.	Unit 2: Testability Measures: SCOAP controllability and observability, High-level testability measures. Combinational Circuit Test Generation: Algorithms and representations, Redundancy identification (RID), Testing as a global problem, Definitions, Test generation systems, Test compaction, Significant combinational ATPG algorithms and sequential circuit test generation.	8



3.	<b>Unit 3: Memory Test:</b> Memory density and defect trends, Faults, Memory test levels, March test notation, Fault modelling, Memory testing. Analog and mixed signal test, Delay test and IDDQ test.	8
4.	Unit 4: Fundamental Techniques for Logic Testing: DFT fundamentals, ATPQ fundamental, Scan architecture and technique	8
5.	Unit 5: Embedded Core Test Fundamentals: Introduction to embedded core testing, Core, Core-based design, Reuse core deliverables, Core DFT issues, Development of reusable core, Scan testing the isolated core, Scan testing the non-core logic, User defined logic chip-level DFT concerns, Memory testing with BIST.	8
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Viswani D. Agarval Michael L. Bushnell, <b>Essentials of electronic testing for</b> digital memory & mixed signal VLSI circuit, Kluwer Academic Publications	I <sup>st</sup>	1999
2.	Alfred L. Crouch, Design for test for digital IC's and embedded core systems, PHI	1 <sup>st</sup>	1999
	Reference Books		
1.	Parag. K. Lala, Digital circuit testing and testability, Academic Press	I <sup>st</sup>	1997
2.	Ashok K. Sharma, <b>Semiconductor memories technology, testing and</b> <b>reliability</b> , Prentice-Hall of India Private Limited, New Delhi	1 <sup>st</sup>	1997

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER II

<i>S. No.</i>	Departm	<b>Department of Electronics and Communication Engineering</b>						
1.	Subject Code	<b>VDM 20</b> 4		VDM 204 Course Title		Low Power VLSI Design		
2.	Contact Hours	L	3		Т	0	Р	0
3.	Examination Duration	Theor	v		3	Practi	cal	0
4.	Relative Weight	CIE	25	5	MSE	25	SEE	50
6.	Credit	03						
6.	Semester	Second						
7.	Category of Course	РС						
8.	Pre-requisite	Advanced Digital Integrated Circuit						

9.	Course Outcomes	After completion of the course the students will be able to: CO1: Acquire the fundamental knowledge of low power VLSI design, CO2: Infer about static and dynamic power dissipation. CO3: Ability to implement logic circuits and advanced low power design
		<i>techniques.</i> <i>CO4: Analyse different techniques required to minimize the leakage power.</i> <i>CO5: Evaluate the characteristics low power analog and digital circuits.</i> <i>CO6: Design of low power memory devices.</i>

<i>S. No.</i>	Contents	Contact Hours
1.	Unit 1: Introduction to Low Power VLSI: Overview, Need for Low Power VLSI Digital Integrated Circuits, Basic Principles of Low Power Design, Physics of Power Dissipation; Technology and Device Effect on Low Power: Transistor Sizing, Gate Oxide Thickness, Impact of Technology Scaling, Technology & Device innovation.	8
2.	Unit 2: Sources of Power Dissipation in MOS Devices: Power Estimation, Dynamic Power Dissipation: Short Circuit Power, Switching Power, Gliching Power; Static Power Dissipation, Probabilistic Power Analysis, Degrees of Freedom.	10
3.	Unit 3: Logic Circuits and Advanced Techniques: Logic circuits, Special Techniques: Architecture and Systems; Emerging Low power Techniques, Physics of Power Dissipation in CMOS FET Devices; Design of Low Power CMOS Circuits, Supply Voltage Scaling Approaches; Switched Capacitance minimization Approaches.	8
4.	Unit 4: Leakage Power Minimization Approaches: Synthesis in Low Power Design, Test of Low Voltages CMOS Circuits; Variable threshold Voltage CMOS (VTCMOS) Approach, Multi threshold Voltage CMOS (MTCMOS)	8



	approach, Power gating Transistor Stacking, Dual- threshold Voltage (Vt) Assignment Approach (DTCMOS).	
5.	Unit 5: Low Power Techniques: Low Power Static RAM Architectures, Low Power SRAM/DRAM Design, Low Energy Computing using Energy Recovery Techniques, Software Design for Low Power, CAD Tools for Low Power Synthesis.	8
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Gary Yeap, "Practical Low Power Digital VLSI Design", Springer.	I <sup>st</sup>	1998
2.	Kaushik Roy and Sharat Prasad, " <b>Low Power CMOS VLSI Circuit Design</b> " Wiley.	I <sup>st</sup>	2000
	Reference Books		
1.	J. B. Kuo and J. H. Lou, Low "Voltage CMOS VLSI Circuits", Wiley.	I <sup>st</sup>	1999
2.	J. M. Rabaey, A. P. Chandrakasan and B. Nikolic, "Digital Integrated Circuits: A Design Perspective",	$2^{nd}$	2003

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER II

<i>S. No.</i>	Departm	ent of Electronics and Communication Engineering					
1.	Subject Code	<b>VDM 2</b> .	51 C	Course Title	Ve	erilog HDL	Lab
2.	Contact Hours	L	0	Т	0	Р	4
3.	Examination Duration	Theor	v	0	Practio	cal	4
4.	Relative Weight	CIE	25	MSE	25	SEE	50
6.	Credit	02					
6.	Semester			Seco	ond		
7.	Category of Course	РС					
8.	Pre-requisite	Digital Electronics					

ſ	9.	Course Outcomes	After completion of the course the students will be able to:
			CO1: Understand digital circuit designing through Verilog HDL.
			CO2: Implement digital logic circuits using Verilog HDL in FPGA.
			CO3: Analyse various combinational and sequential circuits using Verilog
			HDL simulation codes.
			CO4: <b>Design</b> various digital systems using Verilog HDL simulation codes

<b>S</b> . No.	List of problems for which student should develop program and execute in the Laboratory	Contact Hours
1.	Design and simulation of XOR gate using NAND gate only.	2
2.	Design and simulation of comparator.	2
3.	Design and simulation of Full Adder and Full Subtractor.	2
4.	Design and simulation of Multiplexer and Demultiplexer.	2
5.	Design and simulation of Encoder and Decoder.	2
6.	Design and simulation of SR Flip-Flops and D Flip-flop.	2
7.	Design and simulation of JK Flip-Flops and T Flip-flop.	2
8.	Design and simulation of UP-DOWN counter/Decade counter.	2
9.	Design and simulation of different registers.	2
10.	Design and simulation of bidirectional and universal shift register	2
11.	Design and simulation of binary multiplier.	2
12.	FPGA Implementation of basics logic gates.	2
13.	Design and simulation of Finite State Machine (FSM) using "Function" in Verilog.	2



14.	Design and simulation of Finite State Machine (FSM) without using "Function" in Verilog.	2
	Total	28
	Innovative Experiments	
13.	FPGA Implementation of Flip-flops.	2
14.	FPGA Implementation of binary multiplier.	2
15.	Design and simulation of floating-point divider.	2
16.	As suggested by faculty and lab in-charge.	2
	Total	08

11.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	Department of Electronics and Communication Engineering						
<i>1</i> .	Subject Code	VDM 2	R	Course Title	U	Physical De	sign Lab
2.	Contact Hours	L	0	Т	0	Р	4
3.	Examination Duration	Theor	y	0	Practi	cal	4
4.	Relative Weight	CIE	25	MSE	25	SEE	50
6.	Credit			02	2		
6.	Semester			Seco	ond		
7.	Category of Course	РС					
8.	Pre-requisite	Digi	Digital Electronics, Advanced Digital Integrated Circuit				

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Understand Linux environment, tools, and basic scripting.
		CO2: Apply the concepts of physical design for VLSI chip.
		CO3: Analyze placement, routing, and power Planning for different circuits.
		CO4: Design circuits using Verilog HDL, waveform Debugging, and synthesis

10. Details of the Course

S. No.	List of problems for which student should develop program and execute in the Laboratory	Contact Hours
1.	Familiarization with Linux environment, and basic scripting using Verilog HDL.	2
2.	Design, simulation, and test of an 8-bit counter with instructions using Verilog HDL.	2
3.	Synthesis of 8-bit counter circuit with instructions using Verilog HDL.	2
4.	Placement and power planning of 8-bit counter circuit in cadence digital implementation tool of 8-bit counter circuit.	2
5.	Routing of 8-bit counter circuit in cadence digital implementation tool in gpdk 90 technology.	2
6.	Design, simulation, and test of a Half adder with instructions using Verilog HDL.	2
7.	Synthesis of Half adder circuit with instructions using Verilog HDL.	2
8.	Placement and power planning of Half adder circuit in Cadence digital implementation tool of Half adder circuit.	2
9.	Routing of Half adder circuit in Cadence digital implementation tool in gpdk 90 nm technology.	2
10.	Design, simulation, and test of a Full adder with instructions using Verilog HDL.	2

#### SEMESTER II

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11.	Design, simulation, and test of a Half subtractor with instructions using Verilog HDL.	2
12.	Synthesis of Half subtractor circuit with instructions using Verilog HDL.	2
	Total	24
	Innovative Experiments	
13.	Design, simulation, and test of a Full subtractor with instructions using Verilog HDL.	2
14.	Routing of Full subtractor Circuit in Cadence Digital Implementation tool in gpdk 90 nm technology.	2
15.	Design, simulation, and Test of a Full subtractor with instructions using Verilog HDL.	2
	Total	06

<i>11</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER III

<i>S. No.</i>	Departm	<b>Department of Electronics and Communication Engineering</b>						
1.	Subject Code	VDM 3	VDM 351 Course		Modellin	ulation Lab		
2.	Contact Hours	L	0	Т	0	Р	4	
3.	Examination Duration	Theor	v	0	Practi	cal	4	
4.	Relative Weight	CIE	25	MSE	25	SEE	50	
6.	Credit	02						
6.	Semester	Third						
7.	Category of Course	РС						
8.	Pre-requisite	Digi	Digital Electronics, Advanced Digital Integrated Circuit					

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Understand various semiconductor devices and circuit using simulators
		CO2: <b>Compute</b> the characteristics of various digital and analog systems.
		CO3: Analyze Cadence, VTCAD and Xilinx tools for the implementation of
		digital and analog circuits
		CO4: <b>Evaluate</b> various MOS devices performance using MATLAB and
		VTCAD

S. No.	List of problems for which student should develop program and execute in the Laboratory	Contact Hours
1.	Study of Cadence tool for the implementation of Multistage Amplifier.	2
2.	Study of Cadence tool for the implementation of analog circuits (CS Amplifier).	2
3.	Implementation of a novel circuit and its performance analysis using Cadence tool (Flip- Flops using pass transistors).	2
4.	Design and simulation of CMOS (NMOS/PMOS) using VTCAD and their characteristics analysis.	2
5.	Design and simulation of Dual Gate MOSFET using VTCAD and their characteristics analysis.	2
б.	Design and simulation of Gate All Around FET (GAA-FET) using VTCAD and their characteristics analysis.	2
7.	Design and simulation of BJT using VTCAD and their characteristics analysis.	2
8.	Study of OrCAD tool for analysis of RC coupled amplifier.	2
9.	To plot the drain characteristics for n-channel MOSFET using MATLAB for implementation of MOSFET models in linear and saturation region.	2
10.	To plot the transfer characteristics for n-channel MOSFET in linear region and extract the various parameters (like threshold voltage ( $V_{th}$ ), Transconductance ( $g_m$ ), Mobility ( $\mu$ ) and on-off current ratio ( $I_{on}/I_{off}$ ) using MATLAB.	2

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11.	To plot the transfer characteristics for n-channel MOSFET in saturation region and extract the various parameters (like threshold voltage ( $V_{th}$ ), Transconductance ( $g_m$ ), Mobility( $\mu$ ) and on-off current ratio ( $I_{on}/I_{off}$ ) using MATLAB.	2
12.	Write a program for the following condition using Xilinx. Government wants to give subsidy to the citizens, so they decided that if income is greater than subsidy then income itself is the final income. Otherwise, subsidy will be added to income to get the total income.	2
	Total	24
	Innovative Experiments	
13.	FPGA implementation of various logic gates in Xilinx tool.	2
14.	Design and Simulation of universal gates in VTCAD tool.	2
15.	Design and Simulation of Tri-Gate in VTCAD tool.	2
	Total	06

11.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER I

S. No.	Departn	ent of Electronics and Communication Engineering							
1.	Subject Code	VDM 191 Course		urse Title	Advanced Nanotechnolo				
2.	Contact Hours	L	3		Т	0	ŀ	)	0
3.	Examination Duration	Theor	y		3	Practic	al		0
4.	Relative Weight	CIE	25	5	MSE	25	SE	EE	50
6.	Credit	03							
6.	Semester	First							
7.	Category of Course	РЕ							
8.	Pre-requisite		Physics, Chemistry						

9.	Course Outcomes	After completion of the course the students will be able to: CO1: <b>Remember</b> the concepts of emerging world of nanoscience, Knowledge of
		single-electron devices and carbon based nanoelectronics devices.
		CO2: Understand the various top-down and bottom-up approaches for
		nanomaterial synthesis.
		<i>CO3: Apply</i> the acquired knowledge to develop novel nanomaterials.
		CO4: Analyze the properties of nanomaterials using various scanning probe
		techniques and spectroscopic techniques for material characterization.
		CO5: Evaluate the performance of nanotechnology related devices for various
		industrial applications.
		CO6: Utilize analytical tools in nanoscale engineering.

<i>S. No.</i>	Contents	<b>Contact Hours</b>
1.	<i>Unit 1: Introduction to Nanotechnology:</i> <i>Overview, Historical background, Importance of nanoscale, Bottom-up approaches, Top-</i> <i>down approaches, Functional approaches.</i>	8
2.	<i>Unit 2: Nano Materials:</i> <i>Fundamental concepts of nanomaterials, Allotropes of carbon, Graphene, Graphene nanoribbons, Fullerenes, Fullerites, Carbon nanotubes (CNTs), Bucky paper.</i>	8
3.	Unit 3: Nano Electronics: Approaches to Nano electronics, Fabrication of integrated circuits, Introduction to microelectromechanical systems (MEMS), Nanoelectromechanical systems (NEMS), Nanowires, Nano-Circuits, Quantum wire, Quantum well.	10
4.	Unit 4: Nano-Engineering Devices and Nano- Medicine: Lab on chip, Micromachinery, Nanomotor, Nanopore, Nano sensor, Quantum point contact, Synthetic molecular motors, Medical applications of nanomaterials.	8
5.	Unit 5: Analytical Tools in Nanoscale Engineering and Nanolithography: Atomic force microscopy (AFM), Scanning tunnelling microscope (STM), Nanolithography: Dip-pen, Electron beam, Ion-beam sculpting, Nanoimprint lithograph, Photolithography.	10



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Total 44

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Shunri Oda, David Ferry, "Nanoscale Silicon Devices", CRC Press, Taylor & Francis Group.	$I^{st}$	2016
2.	Robert Puers, "Nanoelectronics: Materials, Devices, Applications", Wiley.	I <sup>st</sup>	2017
	Reference Books		
1.	Suprio Datta, "Lessons from nanoelectronics", World Scientific publisher.	I <sup>st</sup>	2012
2.	Gabriel M. Rebeiz, " <b>RF MEMS: Theory, Design, and Technology</b> ", Wiley.	$I^{st}$	2003
3.	Julian W. Gardner, "Microsensors, MEMS and Smart Devices", Wiley.	$I^{st}$	2002

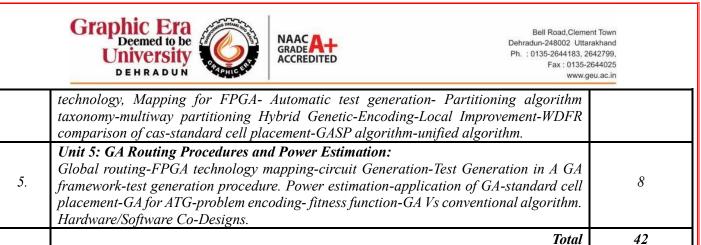
12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SE	MEST	ER I				
<i>S. No</i> .	Departm	epartment of Electronics and Communication Engineering						
1.	Subject Code	VDM 1	VDM 192 Course Title			Optimi	hniques in ign	
2.	Contact Hours	L	3	}	Т	0	Р	0
3.	Examination Duration	Theory	V		3	Practi	cal	0
4.	Relative Weight	CIE	2.	5	MSE	25	SEE	50
6.	Credit				0.	3		
6.	Semester	First						
7.	Category of Course	РЕ						
8.	Pre-requisite			VL	SI Technolo	gy and De	sign	

9.	Course Outcomes	After completion of the course the students will be able to: CO1: <b>Recall</b> the knowledge of modelling techniques based on incorporating empirical parameters. CO2: <b>Understand</b> the performance parameters and yield estimation of optimization techniques. CO3: <b>Apply</b> the knowledge of convex optimization techniques. CO4: <b>Analyse</b> and understand Genetic algorithm in VLSI design.
		CO4: Analyse and understand Genetic algorithm in VLSI design. CO5: Assess and evaluate FPGA for automatic test generation.
		CO6: Implement optimization techniques in VLSI design.

<i>S. No.</i>	Contents	Contact Hours
1.	Unit 1: Statistical Modelling: Modelling sources of variations, Monte Carlo techniques, Process variation modelling- Pelgrom's model, Principal component-based modelling, Quad tree based modelling, Performance modelling-response Surface methodology, Delay modelling, Interconnect delay models.	8
2.	Unit 2: Statistical Performance, Power and Yield Analysis: Statistical timing analysis, Parameter space techniques, Bayesian networks leakage models, High level statistical analysis, Gate level statistical analysis, Dynamic power, Leakage power, Temperature and power supply variations, High level yield estimation and Gate level yield estimation.	8
3.	<b>Unit 3: Convex Optimization:</b> Convex sets, Convex functions, Geometric programming, Trade-off and sensitivity analysis, Generalized geometric programming, Geometric programming applied to digital circuit gate sizing, Floor planning, Wire sizing, Approximation and fitting- monomial fitting, Maxmonomial fitting, Posynomial fitting.	9
4.	<b>Unit 4: Genetic Algorithm:</b> Introduction, GA Technology-Steady state algorithm-Fitnessscaling- Inversion GA for VLSI design, Layout and test automation- Partitioning-automatic placement, Routing	9



S. No.	Name of Authors/Books/Publishers		Year of Publication / Reprint
	Textbooks		
1.	Ashish Srivastava, Dennis Sylvester, David Blaauwi, "Statistical Analysis and Optimization for VLSI: Timing and Power", Springer.	1 <sup>st</sup>	2005
2.	Kalyanmoy Dev, " <b>Optimization for Engineering Design: Algorithms and Examples</b> ", PHI Learning.	$2^{nd}$	2001
	Reference Books		
1.	PinakiMazumder, E. Mrudnick, "Genetic Algorithm for VLSI Design, Layout and test Automation", Prentice Hall.	$I^{st}$	2002

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SE	MEST	ER I					
<i>S. No.</i>	Departm	ent of Elec	tronic	s and	Communica	tion Engi	neering		
1.	Subject Code	VDM 193Course TitleTheory and ApplicationEmbedded System							
2.	Contact Hours	L	Ĵ	}	Т	0	Р		0
3.	Examination Duration	Theor	v		3	Practical		0	
4.	Relative Weight	CIE	2	5	MSE	25	SEI	E	50
6.	Credit				0.	3			
6.	Semester		First						
7.	Category of Course	РЕ							
8.	Pre-requisite		M	icroco	ontrollers &	Embeddea	l System:	5	

9.	Course Outcomes	After completion of the course the students will be able to:		
		CO1: <b>Recall</b> the basic concept of embedded system.		
		CO2: Understand the architecture and instruction sets of PIC microcontrollers.		
		CO3: <b>Relate</b> the knowledge of system firmware design.		
		CO4: Analyse structure of RTOS based embedded systems.		
		CO5: Evaluate ARM-32 bit processors as the advanced series microcontroller.		
		CO6: Integrate the concepts of advanced embedded systems for developing		
		projects.		

<i>S. No.</i>	Contents	Contact Hours
1.	<b>Unit 1: Embedded Systems:</b> Embedded vs General computing system, classification, application and purpose of Embedded system. Core of an Embedded System, Memory, Sensors, Actuators. Characteristics and quality attributes of embedded systems.	8
2.	<i>Unit 2: PIC Architectures:</i> PIC series of microcontrollers, Assembly basics, Instruction list and description, Addressing modes, Interrupts and timer.	8
3.	<b>Unit 3: System Firmware Design:</b> Hardware Software Co-Design, embedded firmware design approaches, computational models, embedded firmware development languages, Integration and testing of Embedded Hardware and firmware.	8
4.	<b>Unit 4: RTOS Based Embedded System Design</b> : Basics of Operating systems, Types of Operating Systems, Tasks, Process and Threads, Multiprocessing and Multitasking, Task Scheduling.	8
5.	Unit 5: ARM-32 bit Microcontroller: Thumb-2 technology and applications of ARM, Architecture of ARM Cortex M3, Various Units in the architecture, General Purpose Registers, Special Registers, exceptions, interrupts, stack operation.	8
	Total	40



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S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Raj Kamal, "Microcontrollers: Architecture, Programming, Interfacing and System Design", Pearson Education India.	$2^{nd}$	2005
2.	J. Morton, "The PIC Microcontroller", Newnes.	3 <sup>rd</sup>	2005
	Reference Books		
1.	A. Sloss, D. Symes, C. Wright, "Arm System Developer's Guide: Designing and optimizing system software", Morgan Kauffman Publisher.	I <sup>st</sup>	2004
2.	K. V. Shibhu, "Introduction to Embedded Systems", Tata McGraw Hill.	$I^{st}$	2009
3.	Frank Vahid, Tony Givargis, "Embedded System Design, A Unified Hardware, Software Approach", Wiley Publications.	3 <sup>rd</sup>	1999

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SE	MEST	ER I					
<i>S. No</i> .	Departm	ent of Elec	etronic.	s and	Communic	ation Engi	neering		
1.	Subject Code	VDM 194 Course Title Digital Signal Proce						ssing for	
2.	Contact Hours	L	Ĵ	8	Т	0	P	,	0
3.	Examination Duration	Theor	y		3	Practical 0		0	
4.	Relative Weight	CIE	2	5	MSE	25	SE	E	50
6.	Credit		<u>u</u>		0	3	<u> </u>		
6.	Semester				Fi	rst			
7.	Category of Course	РЕ							
8.	Pre-requisite		Digital Signal Processing						

9.	Course Outcomes	After completion of the course the students will be able to:	
		<i>CO1:</i> <b>Recall</b> the basic concepts of DFT- FFT in FIR filters and IIR filters.	
		CO2: Understand iteration bound, pipelining and parallel processing.	
		CO3: Apply the knowledge of retiming and parallel processing by using various	
		fast convolution techniques.	
		<i>CO4: Analyse</i> algorithmic strength reduction in filters transforms and pipelined	
		and parallel recursive filters.	
		<i>CO5</i> : <i>Evaluate</i> scaling and round off noise computation processes.	
		CO6: <b>Design</b> and develop high-speed VLSI based devices.	

<i>S. No.</i>	Contents	<b>Contact Hours</b>
1.	<b>Unit 1: Introduction:</b> Linear system theory- Convolution- Correlation - DFT- FFT- Basic concepts in FIR filters and IIR filters- Filter realizations. Representation of DSP algorithms-block diagram-SFG- DFG.	8
2.	Unit 2: Iteration Bound: Data-Flow graph representations, Loop bound and iteration bound, Algorithms for computing iteration bound, Iteration bound of multi-rate data-flow graph. Pipelining and parallel processing: Pipelining of FIR digital filters, Parallel processing, Pipelining and parallel processing for low power.	8
3.	Unit 3: MOS Logic Circuits: Combinational MOS logic circuits: MOS logic circuit with depletion NMOS loads, CMOS logic circuits, Complex logic circuits, CMOS transmission gates. Sequential MOS logic circuits: Behaviour of bistable elements, SR latch, Clocked latch and Flip-flop, CMOS D latch and Flip-flop.	8
4.	Unit 4: Dynamic Logic Circuits: Basic principles of pass transistor circuits, Voltage bootstrapping, Synchronous dynamic circuit techniques, Dynamic CMOS circuit, High performance dynamic CMOS circuits.	9
5.	<b>Unit 5: Low Power CMOS Logic Circuits:</b> Overview of power consumption, Low power design through voltage scaling, Estimation and optimization of switching activity, Reduction of switched capacitance, Adiabatic logic circuits.	9



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Total 42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	K. K. Parhi, "VLSI Digital Signal Processing", John-Wiley	$I^{st}$	1999
2.	John G. Proakis, Dimitris G. Manolakis, "Digital Signal Processing", Prentice Hall of India.	3 <sup>rd</sup>	1996
	Reference Books		
1.	Richard J. Higgins, "Digital signal processing in VLSI", Prentice Hall.	$I^{st}$	1990

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER I

<i>S. No.</i>	Departm	nent of Electronics and Communication Engineering							
1.	Subject Code	VDM 195 Cour		VDM 195 Course Title		<b>Robust Control System</b>			ystem
2.	Contact Hours	L	3		Т	0 P		)	0
3.	Examination Duration	Theor	y	3		Practical		0	
4.	Relative Weight	CIE	25		MSE	25	SE	EE	50
6.	Credit	03							
6.	Semester	First							
7.	Category of Course	РЕ							
8.	Pre-requisite	Control Systems							

9.	Course Outcomes	After completion of the course the students will be able to:			
		CO1: <b>Explain</b> the motivation of robust control.			
		CO2: Compute nominal stability and performance along with robust stability			
		and performance			
		O3: <i>Explain</i> robustness and uncertainty of systems.			
		CO4: <b>Explain</b> robust stability and loop shaping.			
		CO5: Acquire the fundamentals of H2 and $H\infty$ control.			
		CO6: <b>Design</b> feedback control systems			

<i>S. No.</i>	Contents	Contact Hours
1.	<i>Unit 1: Introduction and Background:</i> <i>Control System representations, System stabilities, Coprime factorization and stabilizing</i> <i>controllers, signals and systems norms.</i>	8
2.	<b>Unit 2: Modeling of uncertain systems</b> : Introduction to concepts of model uncertainty, including both parametric and dynamic uncertainty, Linear fractional transformations and canonical forms.	8
3.	<b>Unit 3: Robustness Problems:</b> Linear fractional transformations and canonical forms. Performance measured via (induced) norms. Robust stability and performance problems. Solution of SISO robustness problems.	8
4.	Unit 4: Computer-Aided Analysis Techniques: Introduction to the structured singular value for robustness analysis of MIMO systems. Conversion of robustness problems to canonical $M$ - $\Delta$ form. The small gain theorem and approximate computation of $\mu$ via efficient upper and lower bounds. Computer-aided tools for $\mu$ -analysis based on the Matlab Robust Control Toolbox.	10
5.	Unit 5: Synthesis and Controller: Design Optimal controller design including $H_2$ and $H_{infinity}$ optimal control. Scaled $H_{infinity}$ - optimal control problems and $\mu$ -synthesis. Computer-aided tools to implement D,G-K iteration for advanced controller design. Lower order controllers: Absolute error	10



approximation methods, reduction via fractional factors, relative error approximation methods, and frequency weighted approximation methods, Design case studies.	
Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	U. Mackenroth, "Robust Control Systems-Theory and Case Studies", Springer International Edition.	$I^{st}$	2003
2.	Kemin Zhou, "Essentials of Robust Control", Prentice-Hall.	$I^{st}$	2006
3.	<i>Gu,</i> Da-Wei, <i>Petkov,</i> Petko, <i>Konstantinov</i> , Mihail M, "Robust Control Design with MATLAB", Springer International Edition.	$2^{nd}$	2014
	Reference Books		
1.	Richard.C.Dorf and R.T Bishop, "Modern Control System", P.H.I	$I^{st}$	1994
2.	S P Bhattacharya, L H Keel, H Chapellat, " <b>Robust Control: The Parametric</b> Approach", Prentice-Hall.	$2^{nd}$	1995
3.	P C Chandrasekharan, " <b>Robust Control of Linear Dynamical Systems</b> ", Academic Press.	3 <sup>rd</sup>	1996
4.	<i>R. Jacob Baker, "CMOS: circuit design, layout, and simulation", John Wiley &amp; Sons.</i>	$I^{st}$	2002

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SE	MEST	ER I					
<i>S. No.</i>	Departm	nent of Electronics and Communication Engineering							
1.	Subject Code	VDM 1	96	Со	urse Title	Control of Advanced Electric Machine			
2.	Contact Hours	L	3	•	Т	0 P		9 0	
3.	Examination Duration	Theor	y	3		Practical		0	
4.	Relative Weight	CIE	2:	5	MSE	25	SE	E 50	
6.	Credit		<u>u</u>		0	3	<u> </u>		
6.	Semester		First						
7.	Category of Course	РЕ							
8.	Pre-requisite	Basic Electrical Engineering							

9.	Course Outcomes		
		associated with rotating machines CO6: <b>Summarize</b> the various performance characteristics of special electrical machines.	

<i>S. No.</i>	Contents	Contact Hours
1.	Unit 1: Stepper Motors: Constructional features, principle of operation, modes of excitation, single phase stepping motors, torque production in variable Reluctance (VR) stepping motor, Dynamic characteristics, Drive systems and circuit for open loop control, Closed loop control of stepping motor, control of stepper motor using microcontroller.	10
2.	<i>Unit 2: Switched Reluctance Motors:</i> <i>Constructional features, principle of operation. Torque equation, Power controllers,</i> <i>Characteristics and control. Microprocessor based controller. Sensor less control.</i>	10
3.	Unit 3: Synchronous Reluctance Motors-Constructional features: Axial and radial air gap Motors. Operating principle, reluctance torque – Phasor diagram, motor characteristics.	10
4.	Unit 4: Permanent Magnet Brushless DC Motors: Commutation in DC motors, Difference between mechanical and electronic commutators, Hall sensors, Optical sensors, Multiphase Brushless motor, Square wave permanent	6



	magnet brushless motor drives, Torque and EMF equation, Torque-speed characteristics, Controllers-Microprocessor based controller. Sensorless control.	
5.	<i>Unit 5: Emerging Trends and Applications:</i> <i>Advanced control techniques, sensor less control, model predictive control, direct torque control, field-oriented control, converter control, fault diagnosis and fault-tolerant control, and emerging trends in the field.</i>	6
	Total	42

S. No.	Name of Authors/Books/Publishers		Year of Publication / Reprint
	Textbooks		
1.	Kenjo T., Sugawara A, "Stepping Motors and their Microprocessor Control", Clarendon Press, Oxford.	$I^{st}$	1994
2.	Miller T. J. E., "Switched Reluctance Motor and Their Control", Clarendon Press, Oxford.	I <sup>st</sup>	1993
	Reference Books		
1.	<i>Miller T. J. E., Brushless Permanent Magnet and Reluctance Motor Drives,</i> <i>Clarendon Press, Oxford.</i>	$2^{nd}$	1989
2.	B K Bose, Modern Power Electronics & AC drives, Pearson.	$I^{st}$	2002

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SEA	MESTER	II			
<i>S. No.</i>	S. No. Department of Electronics and Communication Engineering						
1.	Subject Code	VDM 291         Course Title         Micro-Sensors and MEMS				d MEMS	
2.	Contact Hours	L	3	Т	0	Р	0
3.	Examination Duration	Theory	,	3	Practio	cal	0
4.	Relative Weight	CIE	25	MSE	25	SEE	50
6.	Credit			0.	3		
6.	Semester		Second				
7.	Category of Course	РЕ					
8.	Pre-requisite		VLSI Technology				

9.	Course Outcomes	After completion of the course the students will be able to: CO1: Recall the basic principles of different sensors and actuators CO2: Understand the process of miniaturization of a sensor and actuator to produce a micro sensor and micro actuator and its integration with microelectronics circuitry. CO3: Apply various fabrication technologies for miniaturization of sensors and actuators for MEMS. CO4: Analyze the different properties of sensors and actuators. CO5: Evaluate the behavior of MEMS devices. CO6: Create approaches for the designing of different MEMS based devices for
		various real-life applications.

<i>S. No</i> .	Contents	Contact Hours
1.	<b>Unit 1: Microfabrication and Micromachining:</b> Integrated circuit processes, Bulk micromachining, Isotropic etching and anisotropic etching, Wafer bonding, High aspect-ratio processes (LIGA).	10
2.	Unit 2: Physical Micro-Sensors: Classification of physical sensors, Integrated, Intelligent, Smart sensors, Sensor principles and examples: Thermal sensors, Electrical sensors, Mechanical sensors, Chemical and biosensors.	8
3.	<b>Unit 3: Micro actuators:</b> Electromagnetic and thermal micro-actuation, Mechanical design of micro actuators, Micro actuator examples, Microvalves, Micropumps, Micromotors Micro actuator systems, Success stories, Ink-Jet printer heads, Micro-Mirror TV projector.	8
4.	Unit 4: Surface Micromachining: One or two sacrificial layer processes, Surface micromachining requirements, Polysilicon surface micromachining, Other compatible materials, Silicon dioxide, Silicon nitride, Piezoelectric materials, Surface micromachined systems: Success stories, Micromotors, Gear trains mechanisms.	8
5.	Unit 5: Application Areas:	8



All-mechanical miniature devices, 3-D electromagnetic actuators and sensors, RF/Electronics devices, Optical/Photonic devices, Medical devices E.G. DNA-chip, Micro-arrays. MEMS for RF applications: Need for RF MEMS components in communications, Space and defence applications	
Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Chang Liu, "Foundations of MEMS", Pearson.	$2^{nd}$	2012
2.	<i>Rai - Choudhury P., "MEMS and MOEMS Technology and Applications", PHI Learning Private Limited.</i>	$I^{st}$	2009
3.	Julian W. Gardner, "Microsensors, MEMS and Smart Devices", Wiley.	$I^{st}$	2002
	Reference Books		
1.	Gabriel M. Rebeiz, "RF MEMS: Theory, Design, and Technology", Wiley.	$I^{st}$	2003
2.	Stephen D. Senturia, "Microsystem design", Springer.	I <sup>st</sup>	2006

12. Mode og	f Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam
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SEMESTER II

<i>S. No.</i>	<b>Department of Electronics and Communication Engineering</b>							
1.	Subject Code	VDM 292 Course Title		<b>RF</b> Microelectronics Devic				
2.	Contact Hours	L	Ĵ	3	Т	0	Р	0
3.	Examination Duration	Theor	у		3	Practical		0
4.	Relative Weight	CIE	2	5	MSE	25	SEL	E 50
6.	Credit	03						
6.	Semester	Second						
7.	Category of Course	PE						
8.	Pre-requisite	Elect	Electronics Devices and Circuits, Microwave Engineering					

9.	Course Outcomes	After completion of the course the students will be able to:			
		CO1: <b>Recall</b> the concepts of wireless technology in RF design			
		CO2: Understand the modulation techniques for RF circuits.			
		CO3: Apply the basics of detectors and transistor modelling, Mobile RF			
		communication systems and basics of multiple access techniques.			
		CO4: Analyse the concept of BJT and MOSFET behaviour at RF frequencies.			
		CO5: Assess and evaluate Radio frequency devices.			
		CO6: <b>Design</b> and develop RF based microelectronic devices.			

<i>S. No.</i>	Contents	Contact Hours
1.	<b>Unit 1: Introduction:</b> Introduction to RF and wireless technology: Complexity, Design and applications, Choice of technology. Basic concepts in RF design, Nonlinearly and time variance, Random processes and noise.	8
2.	Unit 2: Modulation Techniques for RF Circuits: Definition of sensitivity, Dynamic range, Conversion gains and distortion. Analog and Digital modulation for RF circuits: Comparison of various techniques for power efficiency. Coherent and non-coherent detection.	10
3.	Unit 3: Detectors and Transistor Modelling: Mobile RF communication systems and basics of multiple access techniques. Receiver and transmitter architectures and testing heterodyne, Homodyne, Image-reject, Direct-IF and sub-sampled receivers. Direct conversion and two steps transmitters. BJT and MOSFET behaviour at RF frequencies, Modelling of the transistors and SPICE models.	8
4.	Unit 4: Mixers and Oscillators: Noise performance and limitation of devices. Integrated parasitic elements at high frequencies and their monolithic implementation. Basic blocks in RF systems and their VLSI implementation: Low noise amplifiers design in various technologies, Design of mixers at GHz frequency range. Various mixers, Their working and implementations, Oscillators: Basic topologies VCO and definition of phase noise. Noise-power trade-off. Resonator less VCO design. Quadrature and single-sideband generators.	8



5.	Unit 5: RF Synthesizer: Radio frequency synthesizes: PLLS, Various RF synthesizer architectures and frequency dividers, Power amplifiers design. Linearization techniques, Design issues in integrated RF filters. Some discussion on available CAD tools for RF VLSI designs.	8
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	B. Razavi, " <b>RF Microelectronics</b> ", Prentice-Hall PTR.	$2^{nd}$	2012
2.	<i>T. H. Lee, "The Design of CMOS Radio-Frequency Integrated Circuits", Cambridge University Press.</i>	$I^{st}$	1998
	Reference Books		
1.	<i>R. Jacob Baker, H. W. Li, and D.E. Boyce, "CMOS circuit design, Layout and simulation", Prentice-Hall of India.</i>	$I^{st}$	1998

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	<b>Department of Electronics and Communication Engineering</b>						
1.	Subject Code	VDM 29.	293 Course Title		VLSI Circuits for Biomedical Application		
2.	Contact Hours	L	3	Т	0	Р	0
3.	Examination Duration	Theory	,	3	Practio	cal	0
4.	Relative Weight	CIE	25	MSE	25	SEE	50
6.	Credit			0	3		
6.	Semester	Second					
7.	Category of Course	РЕ					
8.	Pre-requisite	Advanced VLSI Circuit Design, CMOS Analog Circuit Design					

9.	Course Outcomes	After completion of the course the students will be able to: CO1: <b>Recall</b> the concepts of neurochemical and neuro potential devices. CO2: <b>Understand</b> the mechanisms involved in the design of CMOS circuits for implantable biomedical devices and wireless biomedical applications.			
		CO3: Analyze CMOS circuits for wireless medical application.			
		CO4: Apply microneedles and their interfacing with neural systems.			
		CO5: Evaluate the process of neuro-signal acquisition and amplification,			
		neurochemical signal recording, and neuro stimulation.			
		CO6: <b>Develop</b> CMOS circuits for biomedical applications.			

10. Details of the Course

<i>S. No.</i>	Contents	Contact Hours
1.	Unit 1: Introduction: Wireless integrated neurochemical and neuropotential circuits: Introduction, Neurochemical sensing, Neuropotential sensing, RF telemetry and power harvesting in implanted devices, Multimodal electrical and chemical sensing. Visual cortical neuroprosthesis: A system approach: Introduction, System architecture, Prosthesis exterior body unit and wireless link, Body implantable unit, System prototype.	9
2.	Unit 2: CMOS Circuits for Biomedical Implantable Devices: Introduction, Inductive link to deliver power to implants, High data rate transmission through inductive links, Energy and bandwidth issues in multi-channel bio-potential recording. Towards self-powered sensors and circuits for biomedical implants: Introduction, Stress, Strain and fatigue predication, In vivo strain measurement and motivation. Fundamental of piezoelectric-transduction and power delivery, Sub-microwatt piezo-powered VLSI circuits.	9
3.	<b>Unit 3: CMOS Circuits for Wireless Medical Application:</b> Introduction, Spectrum regulations for medical use, Integrated receiver and transmitter architecture, Radio architecture, System budget, Low noise amplifier, Mixer, Polyphase filter, Power amplifier, PLL. Error correcting codes for in vivo RF wireless links.	8

#### SEMESTER II



4.	<b>Unit 4: Microneedles:</b> Introduction, Fabrication methods for hollowout–of–plane microneedles, Application for microneedles. Integrated circuit for neural interfacing: Introduction, nature of neural signals, Neural signal amplification.	8
5.	Unit 5: Integrated Circuits for Neural Applications: Integrated circuit for neural interfacing (Neurochemical recording), Integrated circuit for neural interfacing (Neural Stimulation): Introduction, Electrode configuration and tissue volume conductor, Electrode- Electrolyte Interface, Efficacy, Stimulus generator, Stimulation front end circuits.	8
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Kris Iniewski, "VLSI Circuit Design for Biomedical Application", Artech House Publishers,	I <sup>st</sup>	2008
2.	D. A. Hodges, H. G. Jackson and R. A. Saleh, "Analysis and Design of Digital Integrated Circuits in Deep Submicron Technology", Tata McGraw-Hill,	3 <sup>rd</sup>	2003
	Reference Books		
1.	Parag. K. Lala, "Digital circuit testing and testability", Academic Press.	$I^{st}$	1997
2.	Ashok K. Sharma, "Semiconductor memories technology, testing and reliability", Prentice-Hall of India Private Limited.	$I^{st}$	2002

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	Departm	ent of Electronics and Communication Engineering						
1.	Subject Code	VDM 2	94	Со	urse Title	Microwave & MM-wave Integrated Circuits and Applications		
2.	Contact Hours	L	ź	}	Т	0	Р	0
3.	Examination Duration	Theor	Theory 3		Practical		0	
4.	Relative Weight	CIE	2	5	MSE	25	SEE	50
6.	Credit				03	3		
6.	Semester	Second						
7.	Category of Course	РЕ						
8.	Pre-requisite			Microwave Engineering				

1		
9.	<b>Course Outcomes</b>	After completion of the course the students will be able to:
		<i>CO1: Describe the requirement of MMIC and MM-wave technologies and their various applications.</i>
		CO2: Understand the fabrication processes Circuit of Microwave Integrated
		MIC.
		CO3: <b>Implement</b> the various active and passive circuit elements for microwave and MM-wave technology.
		CO4: Analyze the various measurement systems using MM-wave technology.
		CO5: Evaluate the microwave components for designing microwave Integrated
		circuits.
		CO6: Design of MMIC using MM-Wave Technology.

### 10. Details of the Course

<i>S. No</i> .	Contents	Contact Hours
1.	<b>Unit 1: Introduction</b> : Introduction to Monolithic Microwave Integrated Circuits (MMICs) technology, different types of MMIC, Advantages disadvantages and application of MMICs, MMIC fabrication techniques, Thick and thin film technologies and materials, Encapsulation and mounting of active devices, Introduction to MM-wave integrated circuits, GaAs fabrication technology and various processes, Materials used for MM-wave integrated guides.	10
2.	Unit 2: Passive components: Introduction, Inductors, Capacitors, Resistors, Via-holes, and grounding, Microstrip components, Coplanar circuits, Multilayer techniques, Micromachined passive components.	8
3.	<i>Unit 3: Active Semiconductor circuit elements:</i> <i>Active device technologies and design approaches, Fabrication and modeling: Bipolar junction transistor, Hetero junction bipolar transistor, High electron mobility transistor, MESFET, CMOS, BiCMOS.</i>	10

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4.	<b>Unit 4: Measurement Techniques:</b> Introduction, Test fixture measurements, Probe station measurements, Thermal and cryogenic measurements, Experimental field probing techniques, MM-wave measurement techniques: Electric field probe, Measurement of attenuation constant and guide wavelength. Measurement at radiation loss at bents.	8
5.	<i>Unit 5: System Application:</i> <i>MICs in phased array radars, MICs in satellite television systems, Microwave radio systems, Monolithic MM-wave transceiver.</i>	6
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	I. D. Robertson and S. Lucyszyn, " <b>RFIC and MMIC design and</b> <i>technology</i> ", The Institute of Electrical Engineers.	$2^{nd}$	2001
2.	Leo G. Maloratsk, " <b>Passive RF and Microwave Integrated Circuits</b> ", Elsevier.	$I^{st}$	2004
3.	K. C. Gupta and A. Singh, "Microwave Integrated circuit", John Wiley & Sons.	$2^{nd}$	1974
4.	E. Carey and S. Lidholm, "Millimeter wave Integrated Circuit", Springer.	$2^{nd}$	2005
	Reference Books		
1.	I. Kneppo, J. Fabian, P. Bezousek, P. Hrnicko and M. Pavel, "Microwave Integrated Circuits".	I <sup>st</sup>	1994
2.	S. K. Koul, "Millimeter Wave and Optical Dielectric Integrated Guides and Circuits", John Wiley & Sons.	I <sup>st</sup>	1997
3.	Duixian Liu, Ulrich Pfeiffer, Janusz Grzyb and Brian Gaucher, "Advanced Millimeter-wave Technologies: Antennas, Packaging and Circuits", Wiley.	$I^{st}$	2009

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	Departm	<b>Department of Electronics and Communication Engineering</b>									
1.	Subject Code	VDM 2	VDM 295 Course Title		Renewable Energy Resource and Energy Management						
2.	Contact Hours	L	3	•	Т	0 P		0			
3.	Examination Duration	Theor	y		3	Practio	cal	0			
4.	Relative Weight	CIE	2:	5	MSE	25	SEE	50			
6.	Credit		<u>.</u>		0	3					
6.	Semester	Second									
7.	Category of Course	РЕ									
8.	Pre-requisite				Phy	sics	Physics				

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Describe the knowledge of Solar Power Generation and solar thermal
		applications.
		CO2: Illustrate the photovoltaic characteristics, classifications, fuel cells and
		wind energy systems.
		CO3: <b>Demonstrate</b> the Geothermal energy for conversion in electrical energy.
		CO4: Analyse the performance analysis of Fuel cell and MHD.
		CO5: Evaluate the various renewable power generation techniques and:
		compare the results.
		CO6: <b>Develop</b> solar panels, fuel cells and wind energy techniques.

#### 10. Details of the Course

<i>S. No.</i>	Contents	Contact Hours
1.	<b>Unit 1: Solar Thermal Energy:</b> Solar radiation flat plant collectors and their materials, application and performance, focusing of collectors and their materials, applications and performance solar thermal power plants, thermal energy storage for solar heating and cooling, limitations.	10
2.	Unit 2: Photo voltaic System Solar cell characteristics, solar cell classifications, solar cell module, panel and Array constructions, Maximizing solar PV output and Load Matching, Maximum Power Point Tracking (MPPT), Balance of system components, Solar PV applications	10
3.	Unit 3: Fuel Cells: Principle of working of various types of fuel cells and their working, performance and limitations. Thermo-electrical and thermionic Conversions: Principle of working, performance and limitations	10
4.	Unit 4: Wind Energy: Wind power and its sources, site selection, criterion, momentum theory, classification of rotors, concentrations and augments, wind characteristics. performance and limitations of energy conversion systems.	6

#### SEMESTER II



5.	Unit 5: Geothermal Energy: Resources of geothermal energy, thermodynamics of geo-thermal energy conversion- electrical conversion, non-electrical conversion, environmental considerations. Magneto-hydrodynamics (M H D): Principle of working of M H D Power plant, performance and limitations. Bio-mass: Availability of bio-mass and its convention theory.	6
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	B.H Khan, "Non-Conventional Energy Resources" Tata McGraw-Hill Education.	$2^{nd}$	2000
2.	Max Kurtz, "Handbook of Engineering Economics: Guide for Engineers, Technicians, Scientists, and Managers", McGraw-Hill.	I <sup>st</sup>	1984
3.	A. Mani, " <b>Handbook of solar radiation Data for India</b> ." Allied Publishers Pvt. Ltd.	I <sup>st</sup>	1980
4.	Peter Auer, "Advances in Energy System and Technology", Vol. I & II Edited by Academic Press.	$I^{st}$	1999
5.	F.R. the MITTRE, "Wind Machines" by Energy Resources and Environmental Series". Van Nostrand Reinhold Inc., U.S.	$2^{nd}$	1980
	Reference Books		
1.	Frank Kreith, "Solar Energy Hand Book", Springer.	$I^{st}$	1994
2.	<i>Chermisinogg and Thomes</i> , <i>C. Reign</i> , " <i>Principles and Application of solar Energy</i> ". <i>TMH</i> .	$2^{nd}$	1980

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	Departm	<b>Department of Electronics and Communication Engineering</b>						
1.	Subject Code	VDM 2	VDM 296 Course Title Multivariable Control			rol Systems		
2.	Contact Hours	L	3		Т	0	Р	0
3.	Examination Duration	Theor	y		3	Practical 0		0
4.	Relative Weight	CIE	25	5	MSE	25	SEE	50
6.	Credit	03						
6.	Semester	Second						
7.	Category of Course	РЕ						
8.	Pre-requisite		Basic Electrical Engineering					

9.	Course Outcomes	After completion of the course the students will be able to: CO1: <b>Recall</b> the used of classical control in multivariable systems CO2: <b>Extend</b> the basic knowledge and understanding of the multivariable systems CO3: <b>Implement</b> the multivariable systems through open and closed loop transfer function and study of their behaviour.
		CO4: Analyze a multivariable dynamic system CO5: Evaluate the stability, performance and robustness of a closed-loop system
		CO6: <b>Design</b> an appropriate controller for the multivariable system

10. Details of the Course

<i>S. No.</i>	Contents	<b>Contact Hours</b>
1.	Unit 1: Introduction to Multi-variable systems: Classical feedback control in the multivariable case, Introduction to multivariable control, Elements of linear systems theory, Limitations on performance in SISO and MIMO systems.	8
2.	Unit 2: Analysis of Multi-Variable System: Open loop dynamic analysis in state space, Multi-variable transfer function, Multi variable pole – zero concept, quantitative measure of singularity, closed loop dynamic analysis.	10
3.	Unit 3: Multi – Single loop designs: Preliminary consideration of interaction analysis and loop pairing, the relative gain array, loop pairing using RGA, loop pairing of nonlinear system, loop pairing for system with pure integrator modes, loop pairing for non-square systems, multi-loop controller, controller tuning for multi-loop system.	8
4.	Unit 4: Introduction to De-couplers: Introduction, Decoupling, feasibility of steady state de-coupler design, steady state decoupling by singular value decomposition.	8
5.	Unit 5: Design of multivariable systems:	8

#### SEMESTER II



Multi-loop controller Design procedure, Controller tuning for multi-loop system, Multivariable controller design.	
Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Y. S. Apte, Linear multivariable control system, Tata McGraw Hill.	$I^{st}$	1981
2.	Dale E. Seborg, Thomas F. Edgar, and Duncan A. Mellichamp, <b>Process</b> <b>Dynamics and Control</b> , Wiley India	1 <sup>st</sup>	2003
	Reference Books		
1.	C. T. Chen, Linear system theory and design, Oxford University Press, 1999.	1 <sup>st</sup>	1999
2.	John Bay, Fundamentals of linear state space systems, Tata McGraw Hill, 1998.	$I^{st}$	1998
3.	Wilson Rugh, Linear system theory, Prentice Hall, 1996.	$I^{st}$	1996

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER III

<i>S. No.</i>	Departn	tment of Electronics and Communication Engineering					
1.	Subject Code	VDM 391	! (	Course Title	Organic Electronics Devices and Circuits		
2.	<b>Contact Hours</b>	L	3	Т	0	Р	0
3.	Examination Duration	Theory		3	Practio	cal	0
4.	Relative Weight	CIE	25	MSE	25	SEE	50
6.	Credit		03				
6.	Semester			Th	ird		
7.	Category of Course	РЕ					
8.	Pre-requisite	Basic Elec	Basic Electronics Engineering, Electronics Devices and Circuits.				

9.	Course Outcomes	After completion of the course the students will be able to: CO1: Ability to describe basic concepts and limitations of conventional silicon- based semiconductor devices. CO2: Understand the basic concepts and classification of organic materials. CO3: Apply the advancement of charge transport in organic materials for different organic electronic devices. CO4: Design and develop innovative organic electronic devices. CO5: Evaluate the performance of organic solar cells. CO4: Analyze the different properties of OLED.
		CO6: Analyse the different properties of OLED.

<i>S. No.</i>	Contents	Contact Hours
1.	Unit 1: Organic Materials and Device Physics: Introduction; Organic materials: Conducting polymers and small molecules, Organic semiconductors: p-type and n-type semiconductors, Source, Drain and Gate electrodes, Gate dielectrics, Substrate. Energy band diagram and concept of charge transport in organic semiconductors; Comparison between organic and inorganic semiconductors including the merits, Demerits and limitations.	10
2.	Unit 2: Organic Thin Film Transistors (OTFTs): Introduction; Operating principle; Output and transfer characteristics; Classification of various organic thin film transistors (OTFT) structures; Performance parameters; Impact of structural parameters on behaviour of OTFT; Concept of contact resistance; Single Gate (SG) and Dual Gate (DG) TFT performance comparison; Merits, Demerits, Limitations and future scope. Applications: - Organic complementary inverter circuits; Organic memory - Organic static random-access memory (OSRAM).	8
3.	Unit 3: Organic Light Emitting Diodes (OLEDs) Introduction; Organic materials for OLEDs; Classification of OLEDs, Operating principle; Output and transfer characteristics; Analysis of OLED performance: Optical, Electrical and thermal properties, Merits and demerits; Stability issues; OLEDs as display applications.	8



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4.	Unit 4: Organic Solar Cell: Introduction; Operating principle; Characteristics; Materials for organic solar cells; Classification of organic solar cell- Single layer, Bi-layer and bulk hetero junction organic solar cell; Merits and demerits; Applications and future scope.	8
5.	Unit 5: Organic Sensors: Introduction; Working principle and organic sensing materials for pressure sensors (Piezoresistive, Piezoelectric, and Capacitive sensor), Temperature sensors, Humidity sensors and pH sensor; comparison between organic and conventional sensors including merits, demerits and limitations; Applications of organic sensors; Basics of ionic polymer–metal composites (IPMC) and its applications.	8
	Total	42

S. No.	Name of Authors/Books/Publishers		Year of Publication / Reprint
	Textbooks		
1.	Hagen Klauk, " <b>Organic Electronics: Materials, Manufacturing and</b> <b>Applications</b> ", Wiley-VCH VerlagGmbh& Co. KGaA, Germany, 1 <sup>st</sup> Edition, 2006.	$I^{st}$	2006
2.	Klaus Mullen, UllrichScherf, " <b>Organic Light Emitting Devices: Synthesis,</b> <b>Properties and Applications</b> ", Wiley-VCH VerlagGmbh& Co. KGaA, Germany, 1 <sup>st</sup> Edition, 2005.	1 <sup>st</sup>	2002
3.	Johannes Karl Fink, " <b>Polymeric Sensors and Actuators</b> ", John Wiley & Sons, 1 <sup>st</sup> Edition, 2012.	$I^{st}$	2012
	Reference Books		
1.	Hagen Klauk, " <b>Organic Electronics II: More Materials and Applications</b> ", Wiley-VCH VerlagGmbh& Co. KGaA, Weinheim, Germany.	$I^{st}$	2012
2.	Flora Li, Arokia Nathan, Yiliang Wu, Beng S. Ong, "Organic Thin Film Transistor Integration: A Hybrid Approach", Wiley-VCH, Germany.	1 <sup>st</sup>	2011
3.	Wolfgang Brutting, " <b>Physics of Organic Semiconductors</b> ", Wiley-VCH VerlagGmbh& Co. KGaA, Germany.	$2^{nd}$	2005
4.	Daniel A. Bernards, Róisín M. Owens, George G. Malliaras, " <b>Organic</b> <b>Semiconductors in Sensor Applications</b> ", Springer Science & Business Media.	$I^{st}$	2008

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



SEMESTER III

<i>S. No.</i>	Departm	nent of Electronics and Communication Engineering							
1.	Subject Code	VDM 392         Course Title         Memory Designment				y Design	sign and Testing		
2.	Contact Hours	L	3		Т	0	Р	0	
3.	Examination Duration	Theor	y		3	Practical		0	
4.	Relative Weight	CIE	2.	5	MSE	25	SEE	50	
6.	Credit				0	3			
6.	Semester	Third							
7.	Category of Course	PE							
8.	Pre-requisite	Low Power VLSI Design							

9.	Course Outcomes	After completion of the course the students will be able to:			
		CO1: Acquire the fundamental knowledge of CMOS memory devices.			
		CO2: Infer about configuration of fundamental VLSI chip.			
		CO3: <i>Ability</i> to implement high performance digital VLSI memory systems.			
		CO4: Analyze different techniques required to implement low power memory			
		chip.			
		<i>CO5</i> : <i>Evaluate</i> the characteristics digital VLSI memory systems.			
		CO6: <b>Design</b> of low power memory devices.			

<i>S. No.</i>	Contents	Contact Hours
1.	Unit 1: Introduction to Memory Chip Design: Basics of Semiconductor Memory, Internal Organization of Memory Chips, Memory Cell Array, Peripheral Circuit, I/O Interface Categories of Memory Chip, History of Memory- Cell Development, Architectures of memory cell: SRAM Cell, DRAM Cell Trends in Non- Volatile Memory Design and Technology, Ferroelectric memory, Basic Operation of Flash Memory Cells, Advances in Flash-Memory Design and Technology.	10
2.	Unit 2: Basics of RAM Design and Technology: Devices, NMOS Static Circuits, NMOS Dynamic Circuits, CMOS Circuits, Basic Memory Circuits, Scaling Law. On-Chip Voltage Generators: Substrate-Bias Voltage (VBB) Generator, Voltage Up Converter, Voltage Down-Converter, Half-VDD Generator, Examples of Advanced On-Chip Voltage Generators.	8
3.	Unit 3: DRAM Circuits: High-Density Technology, High-Performance Circuits, Catalog Specifications of the Standard DRAM, Basic Configuration and Operation of the DRAM Chip, Chip Configuration, Address Multiplexing, Fundamental Chip, Multi-divided Data Line and Word Line, Read and Relevant Circuits, Write and Relevant Circuits, Refresh-Relevant Circuits, Redundancy Techniques, On-Chip Testing Circuits, High Signal-to-Noise Ratio	8



	DRAM Design and Technology, Trends in High S/N Ratio Design, Data-Line Noise Reduction, Noise Sources.	
4.	Unit 4: High-Performance Subsystem Memories: Hierarchical Memory Systems, Memory-Subsystem Technologies, High-Performance Standard DRAMs, Embedded Memories. Low-Power Memory Circuits: Sources and Reduction of Power Dissipation in a RAM Subsystem and Chip, Low-Power DRAM Circuits, Low-Power SRAM Circuits.	8
5.	Unit 5: Ultra-Low-Voltage Memory Circuits: Design Issues for Ultra-Low-Voltage RAM Circuits, Reduction of the Subthreshold Current, Stable Memory-Cell Operation, Suppression of, or Compensation for, Design Parameter Variations, Power-Supply Standardization, Ultra-Low Voltage DRAM Circuits, Ultra-Low-Voltage SRAM Circuits, Ultra-Low-Voltage SOI Circuits.	8
	Total	42

S. No.	Name of Authors/Books/Publishers		Year of Publication / Reprint
	Textbooks		
1.	Itoh, K., VLSI Memory Chip Design, Springer,	3rd	2006
2.	Sharma, A. K., Semiconductor Memories: Technology, Testing and <b>Reliability</b> , Wiley- IEEE press, 1 <sup>st</sup> Edition, 2002.	$I^{st}$	2002
	Reference Books		
1.	J. B. Kuo and J. H. Lou, Low "Voltage CMOS VLSI Circuits", Wiley.	$I^{st}$	1999
2.	J. M. Rabaey, A. P. Chandrakasan and B. Nikolic, "Digital Integrated Circuits: A Design Perspective".	$2^{nd}$	2003

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SEN	<i>AESTE</i>	ER III				
S. No.	Departm	ent of Elec	tronic	s and	Communica	tion Engi	neering	
1.	Subject Code	VDM 3	93	Со	urse Title	System	on Chip Testin	Design and g
2.	Contact Hours	L	Ĵ	3	Т	0	Р	0
3.	Examination Duration	Theor	V		3	Practi	cal	0
4.	Relative Weight	CIE	2	5	MSE	25	SEE	50
6.	Credit	03						
6.	Semester	Third						
7.	Category of Course	PE						
8.	Pre-requisite		VLSI Technology					

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Recall the concepts of System-On-Chip (SoC) Testing.
		CO2: Understand the concepts of digital test architectures design.
		CO3: Apply the concepts of SoC on delay testing and low-power testing.
		CO4: Analyze the basics of system/network-on-chip test architectures.
		CO5: Assess and evaluate debug and diagnosis.
		CO6: Implement different testing techniques in SoC.

<i>S. No</i> .	Contents	<b>Contact Hours</b>
1.	Unit 1: Introduction: Importance of system-on-chip testing, Basics of SoC testing, Basics of memory testing, SoC design examples. Digital Test Architectures: Scan design, Logic built-In self-test, Test compression, Random-access scan design. Fault-Tolerant Design: Fundamentals of fault tolerance, Fundamentals of coding theory, Fault tolerance schemes	8
2.	<ul> <li>Unit 2: System/Network-on-Chip Test Architectures: System-on-Chip (SoC) testing, Network-on-Chip (NoC) testing, Design and test practice: Case studies.</li> <li>SIP Test Architectures: Introduction, Bare die, Functional system test, Test of embedded components.</li> <li>Delay Testing:Delay test application, Delay fault models, Delay test sensitization, Delay fault, Delay fault test generation, Pseudo-functional testing to avoid over-testing</li> </ul>	8
3.	Unit 3: Low-Power Testing: Introduction, Energy and power modelling, Test power issues, Low-power scan testing, Low-power built-in self-test, Low-power test data compression, Low-power RAM testing. Coping with Physical Failures, Soft Errors, and Reliability Issues: Signal integrity, Manufacturing defects, Process variations, and Reliability, Soft errors, Defect and error tolerance.	8

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4.	<ul> <li>Unit 4: Design for Manufacturability and Yield:</li> <li>Introduction, Yield, components of yield, Photolithography, DFM and DFY, Variability, Metrics for DFX.</li> <li>Design for Debug and Diagnosis: Introductionto logic design for debug and diagnosis (DFD) structures, Probing technologies, Circuit editing, Physical DFD structures, Diagnosis and debug process.</li> </ul>	8
5.	Unit 5: Software-Based Self-Testing: Introduction, Software-based self-testing paradigm, Processor functional fault self- testing, Processor structural fault self-testing, Processor self-diagnosis, testing global interconnect, testing nonprogrammable cores, Instruction-level DFT, DSP-Based Analog/Mixed-signal component testing. Field Programmable Gate Array Testing: Overview of FPGAs, Testing approaches, BIST of programmable resources, Embedded processor-based testing	10

Total

42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Laung-Terng Wang, Charles E. Stroud, Nur A. Touba, "System-On-Chip Test Architectures (Nanometer Design for Testability)".	Ist	2008
	Reference Books		
1.	<i>Erik Larsson, "Introduction to Advanced system- on- chip test design and optimization", Springer.</i>	$5^{th}$	2006

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



		SEN	<i><b>AESTE</b></i>	ER III					
<i>S. No.</i>	Departm	Department of Electronics and Communication Engineering							
1.	Subject Code	VDM 3	VDM 394Course TitleVLSI Physical Desig Automation				0		
2.	Contact Hours	L	3	•	Т	0	ŀ	)	0
3.	Examination Duration	Theory	V		3	Practio	cal		0
4.	Relative Weight	CIE	2.	5	MSE	25	SE	EE	50
6.	Credit	03							
6.	Semester	Third							
7.	Category of Course	PE							
8.	Pre-requisite	Ba	<b>Basic Electronics Engineering, Digital Electronics.</b>						

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: <b>Recall</b> the concepts of VLSI design automation tools.
		CO2: Understand different layout compaction, placement, and routing
		algorithms.
		CO3: Apply the concepts of Logic Synthesis in VLSI design.
		CO4: Analyze floor planning and routing algorithms.
		CO5: Assess and evaluate scheduling algorithms, allocation, and assignment.
		CO6: Optimize design layouts for floor-planning, placement, and routing

<i>S. No.</i>	Contents	Contact Hours
1.	<i>Unit 1: VLSI Design Automation Tools:</i> Design cycle, Design styles, Algorithms and system design, Structural and logic design, Transistor level design, Layout design, Verification methods, Design management tools.	10
2.	Unit 2: Layout Compaction, Placement and Routing: Design rules, Symbolic layout, Applications of compaction, Formulation methods, Algorithms for constrained graph compaction, Circuit representation, Wire length estimation, Placement algorithms, Partitioning algorithms.	8
3.	<i>Unit 3: Floor Planning and Routing:</i> <i>Floor planning concepts, Shape functions and Floor planning, Sizing, Local routing, Area</i> <i>routing, Channel routing, Global routing and its algorithms.</i>	8
4.	<b>Unit 4: Simulation and Logic Synthesis:</b> Gate level and switch level modelling and simulation. Introduction to combinational logic synthesis, ROBDD principles, Implementation, Construction and manipulation, Logic synthesis.	8
5.	<b>Unit 5: High-Level Synthesis:</b> Hardware model for high level synthesis, Internal representation of input algorithms, Allocation, Assignment and scheduling, Scheduling algorithms. Aspects of assignment.	8
	Total	42



S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	S. H. Gerez, "Algorithms for VLSI Design Automation", John Wiley.	3 <sup>rd</sup>	2000
2.	N. A. Sherwani, "Algorithms for VLSI Physical Design Automation", Kluwer.	3 <sup>rd</sup>	1999
	Reference Books		
1.	M. Sait, H. Youssef, "VLSI Physical Design Automation", World scientific.	$I^{st}$	1999
2.	M. Sarrafzadeh, "Introduction to VLSI Physical Design", McGraw Hill (IE).	$I^{st}$	1996

12.	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	<b>Department of Electronics and Communication Engineering</b>							
1.	Subject Code	VDM 395 Course Title		Power Quality Assessment				
2.	Contact Hours	L	3		Т	0	Р	0
3.	Examination Duration	Theor	y		3	Practic	cal	0
4.	Relative Weight	CIE	25	5	MSE	25	SEE	50
6.	Credit	03						
6.	Semester	Third						
7.	Category of Course	PE						
8.	Pre-requisite	Basic Electrical Engineering						

9.	Course Outcomes	After completion of the course the students will be able to: CO1: <b>Describe</b> the characteristics of ac transmission system, shunt and series reactive compensation. CO2: <b>Understand</b> waveform distortion and processing techniques, and their power assessment concepts. CO3: <b>Demonstrate</b> the working principles of FACTS devices and their operating characteristics.
		CO4: Analyze Static Synchronous Compensator (STATCOM).
		CO5: Estimate the working principles of devices to improve power quality.
		CO6: <b>Propose</b> the power quality monitoring system and their harmonic analysis.

10. Details of the Course

<i>S. No.</i>	Contents	Contact Hours
1.	<b>Unit 1: Introduction:</b> <b>P</b> ower quality-voltage quality-overview of power quality phenomena-classification of power quality issues-power quality measures and standards-THD-TIF-DIN-message weights-flicker factor-transient phenomena-occurrence of power quality problems-power acceptability curves-IEEE guides, EMC standards and recommended practices.	8
2.	Unit 2: Power Assessment under Waveform Distortion & Processing Techniques: Introduction, single phase definitions, three phase definitions, illustrative examples, Fundamental frequency characterization, Fourier analysis, Fast Fourier Transform, Window functions, Efficiency of FFT algorithms, alternative transforms, wavelet transform, Hartely transform, Automation of disturbance recognition.	8
3.	<b>Unit 3: Power Quality Monitoring:</b> Introduction, transducers, CT, PT, power quality instrumentation, Harmonic monitoring, event recording, flicker monitoring, assessment of voltage and current unbalance, examples of application	6
4.	Unit 4: Evaluation of power system harmonic distortion: Introduction, direct harmonic analysis, incorporation of harmonic voltage sources, derivation of network harmonic impedances, solution by direct injection, Representation	6

#### SEMESTER III



	of individual power system components, implementation of harmonic analysis, post processing and display of results.	
5.	<b>Unit 5: Harmonic Mitigation &amp; Grounding:</b> Passive filtering, Harmonic resonance, Impedance Scan Analysis-Active Power Factor Corrected Single Phase Front End, introduction to three Phase APFC and Control Techniques, Grounding and wiring– introduction-NEC grounding requirements-reasons for grounding-typical grounding and wiring problems-solutions to grounding and wiring problems.	8
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Math H. Bollen, "Understanding Power Quality Problems", Wiley-IEEE Press.	Ist	1999
2.	G. T. Heydt Stars "Electric Power Quality", Circle Publishers.	2nd	1994
	Reference Books		
1.	J. Arrillaga, "Power System Quality Assessment". John Wiley.	2nd	2000
2.	Surya Santoso, H. Wayne Beaty, Roger C. Dugan, Mark F. McGranaghan, "Electrical Power System Quality", McGraw Hills.	2nd	2002

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam



<i>S. No.</i>	Departm	ment of Electronics and Communication Engineering						
1.	Subject Code	VDM 396 Course Title		<b>Optimal &amp; Adaptive Control</b>				
2.	Contact Hours	L	3		Т	0	Р	0
3.	Examination Duration	Theor	y		3	Practio	cal	0
4.	Relative Weight	CIE	25	5	MSE	25	SEE	50
6.	Credit	03						
6.	Semester	Third						
7.	Category of Course	РЕ						
8.	Pre-requisite	Basic Electrical Engineering						

9.	Course Outcomes	After completion of the course the students will be able to:
		CO1: Describe performance index and to define various optimal control
		problems.
		CO2: Extend knowledge of discrete linear regulator problem using dynamic
		programming.
		CO3: Apply the conditions for optimality and to solve continuous time linear
		regulator problem.
		CO4: <i>Examine</i> minimum time and minimum control effort problems.
		CO5: Evaluate adaptive control problems and to learn the mathematical
		description of model reference adaptive systems.
		CO6: <b>Design</b> adaptive systems using various techniques.

#### 10. Details of the Course

<i>S. No.</i>	Contents	Contact Hours
Ι.	<ul> <li>Unit 1: Problem Formulation: Mathematical model, Physical constraints, Characteristics of the plants, Performance Measure, optimal control problems, selection of performance measure, state regulator problem, output regulator problem.</li> <li>Calculus of Variations: Fundamental concepts, minimization of functions, minimization of Functionals, Lagrange multiplier approach, constrained extrema, Variational approach to optimal control problems, formulation of variational calculus using Hamiltonian Method.</li> </ul>	09
2.	Unit 2: Dynamic Programming: Optimal control law, Principle of optimality, principle of causality, principle of invariant imbedding, a recurrence relation of dynamic programming – computational procedure, Hamilton-Jacobi equation, and its application, one dimensional regulator problem and its solution using dynamic programming computational procedure.	08
3.	Unit 3: Optimization Problems & Techniques: Pontryagin's minimum principle, control & state variable inequality constraints, A nonlinear Reactor model problem and its solution, Minimum time problems, Minimization of functions, minimization of Functionals, two point boundary value problems.	08

#### SEMESTER III



4.	<b>Unit 4:</b> Adaptive Control (Identifier based & Non Identifier based): Applications, Linear feedback, effects of process disturbances, robustness, adaptive schemes and various adaptive control strategies, Parametric models, Parameter identification (One Parameter Case & two Parameter Case).	08
5.	Unit 5: Model – Reference Adaptive System (MRAS) & Gain Scheduling:- MRAS: MIT Rule, Lyapunov Theory, Design of MRAS using Lyapunov Theory, Relation between MRAS and STR, Non-Linear System: Feedback Linearization, Adaptive Feedback Linearization, Back-stepping, Adaptive Back-stepping with tuning functions, Design of Gain- Scheduling Controllers.	09
	Total	42

S. No.	Name of Authors/Books/Publishers	Edition	Year of Publication / Reprint
	Textbooks		
1.	Donald E. Kirk, " <b>Optimal Control Theory: An Introduction</b> ", Prentice-Hall networks series, 10th Edition, 1970.	$I^{st}$	1970
2.	Anderson B. D. O, Moore J. B, " <b>Optimal control linear Quadratic methods</b> ", <i>Prentice Hall of India</i> ,	$I^{st}$	1991
	Reference Books		
1.	Sage A. P, White C. C, "Optimum Systems Control" Prentice Hall.	$2^{nd}$	1977
2.	Athans M and P L Falb, " <b>Optimal Control-An Introduction to the Theory</b> and its Applications", McGraw Hill Inc,	$2^{nd}$	1966

<i>12</i> .	Mode of Evaluation	Test / Quiz / Assignment / Mid Term Exam / End Term Exam